

MOS INTEGRATED CIRCUIT

μ PD42S16160L, 4216160L, 42S18160L, 4218160L

3.3 V OPERATION 16M-BIT DYNAMIC RAM

1M-WORD BY 16-BIT, FAST PAGE MODE, BYTE READ/WRITE MODE

DESCRIPTION

The μ PD42S16160L, 4216160L, 42S18160L, 4218160L are 1 048 576 words by 16 bits dynamic CMOS RAMs.

These differ in refresh cycle and the μ PD42S16160L, 42S18160L can execute $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh (see the table below).

These are packed in 50-pin plastic TSOP(II) and 42-pin plastic SOJ.

FEATURES

- 1 048 576 words by 16 bits organization
- Single +3.3 V $\pm$ 0.3 V power supply
- Fast page mode
- Byte read/write mode
- The μ PD42S16160L, 42S18160L can execute $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh.

Part number	Refresh cycle	Refresh	Power consumption at standby (MAX.)
μ PD42S16160L	4 096 cycles/128 ms	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, $\overline{\text{RAS}}$ only refresh, hidden refresh	0.54 mW (CMOS level input)
μ PD42S18160L	1 024 cycles/128 ms		
μ PD4216160L	4 096 cycles/64 ms	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, $\overline{\text{RAS}}$ only refresh, hidden refresh	1.8 mW (CMOS level input)
μ PD4218160L	1 024 cycles/16 ms		

- Fast access and cycle time

Part number	Power consumption Active (MAX.)	Access time (MAX.)	R/W cycle time (MIN.)	Fast page mode cycle time (MIN.)
μ PD42S16160L-A60, 4216160L-A60	324 mW	60 ns	110 ns	40 ns
μ PD42S18160L-A60, 4218160L-A60	540 mW			
μ PD42S16160L-A70, 4216160L-A70	288 mW	70 ns	130 ns	45 ns
μ PD42S18160L-A70, 4218160L-A70	504 mW			
μ PD42S16160L-A80, 4216160L-A80	252 mW	80 ns	150 ns	50 ns
μ PD42S18160L-A80, 4218160L-A80	468 mW			

The information in this document is subject to change without notice.

ORDERING INFORMATION

Part number	Access time (MAX.)	Package	Refresh
μPD42S16160LG5-A60	60 ns	50-pin plastic TSOP (II) (400 mil) Normal pinout	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh $\overline{\text{RAS}}$ only refresh Hidden refresh
μPD42S18160LG5-A60			
μPD42S16160LG5-A70	70 ns		
μPD42S18160LG5-A70			
μPD42S16160LG5-A80	80 ns		
μPD42S18160LG5-A80			
μPD42S16160LG5M-A60	60 ns	50-pin plastic TSOP (II) (400 mil) Reverse pinout	
μPD42S18160LG5M-A60			
μPD42S16160LG5M-A70	70 ns		
μPD42S18160LG5M-A70			
μPD42S16160LG5M-A80	80 ns		
μPD42S18160LG5M-A80			
μPD42S16160LLE-A60	60 ns	42-pin plastic SOJ (400 mil)	
μPD42S18160LLE-A60			
μPD42S16160LLE-A70	70 ns		
μPD42S18160LLE-A70			
μPD42S16160LLE-A80	80 ns		
μPD42S18160LLE-A80			
μPD4216160LG5-A60	60 ns	50-pin plastic TSOP (II) (400 mil) Normal pinout	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh $\overline{\text{RAS}}$ only refresh Hidden refresh
μPD4218160LG5-A60			
μPD4216160LG5-A70	70 ns		
μPD4218160LG5-A70			
μPD4216160LG5-A80	80 ns		
μPD4218160LG5-A80			
μPD4216160LG5M-A60	60 ns	50-pin plastic TSOP (II) (400 mil) Reverse pinout	
μPD4218160LG5M-A60			
μPD4216160LG5M-A70	70 ns		
μPD4218160LG5M-A70			
μPD4216160LG5M-A80	80 ns		
μPD4218160LG5M-A80			
μPD4216160LLE-A60	60 ns	42-pin plastic SOJ (400 mil)	
μPD4218160LLE-A60			
μPD4216160LLE-A70	70 ns		
μPD4218160LLE-A70			
μPD4216160LLE-A80	80 ns		
μPD4218160LLE-A80			

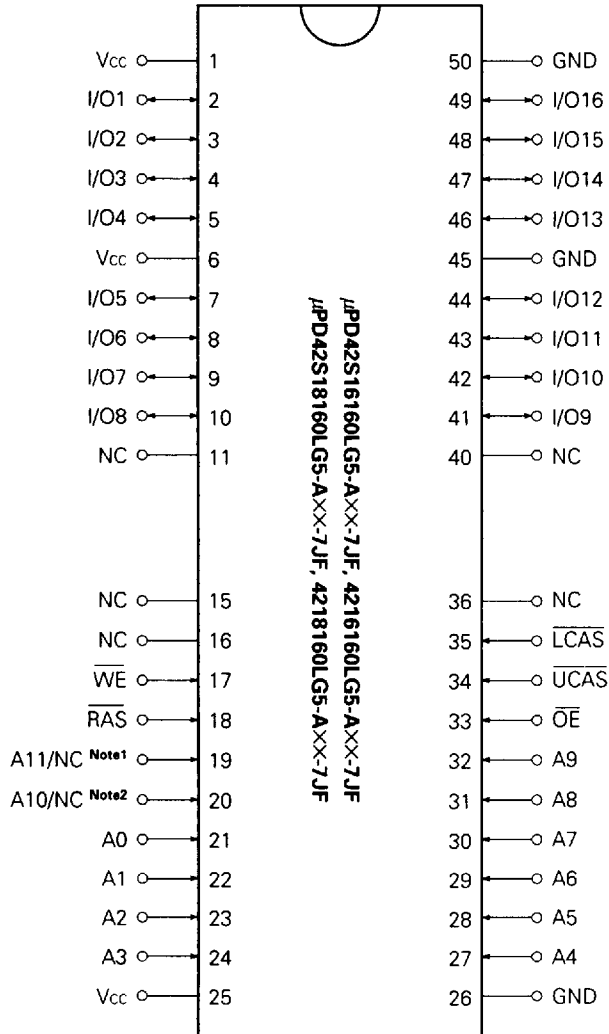
QUALITY GRADE

STANDARD

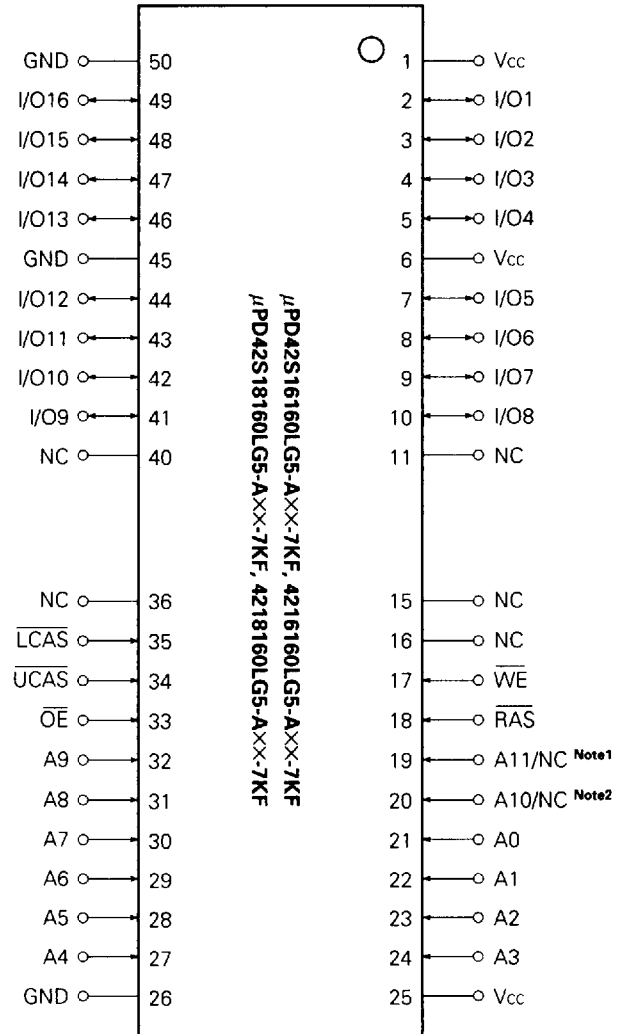
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number I EI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

PIN CONFIGURATIONS (Marking side)

50-pin Plastic TSOP (II)



Reverse bent



Notes 1. A11 . . . μPD42S16160L, 4216160L

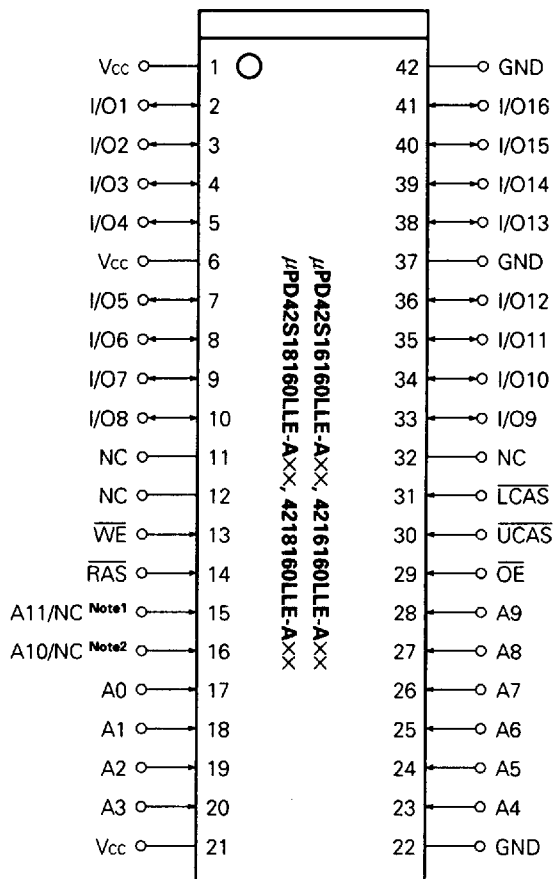
NC . . . μPD42S18160L, 4218160L

2. A10 . . . μPD42S16160L, 4216160L

NC . . . μPD42S18160L, 4218160L

- A0 to A11 : Address Inputs
- I/O1 to I/O16 : Data Inputs/Outputs
- RAS : Row Address Strobe
- UCAS : Column Address Strobe (upper)
- LCAS : Column Address Strobe (lower)
- WE : Write Enable
- OE : Output Enable
- Vcc : Supply Voltage
- GND : Ground
- NC : No Connection

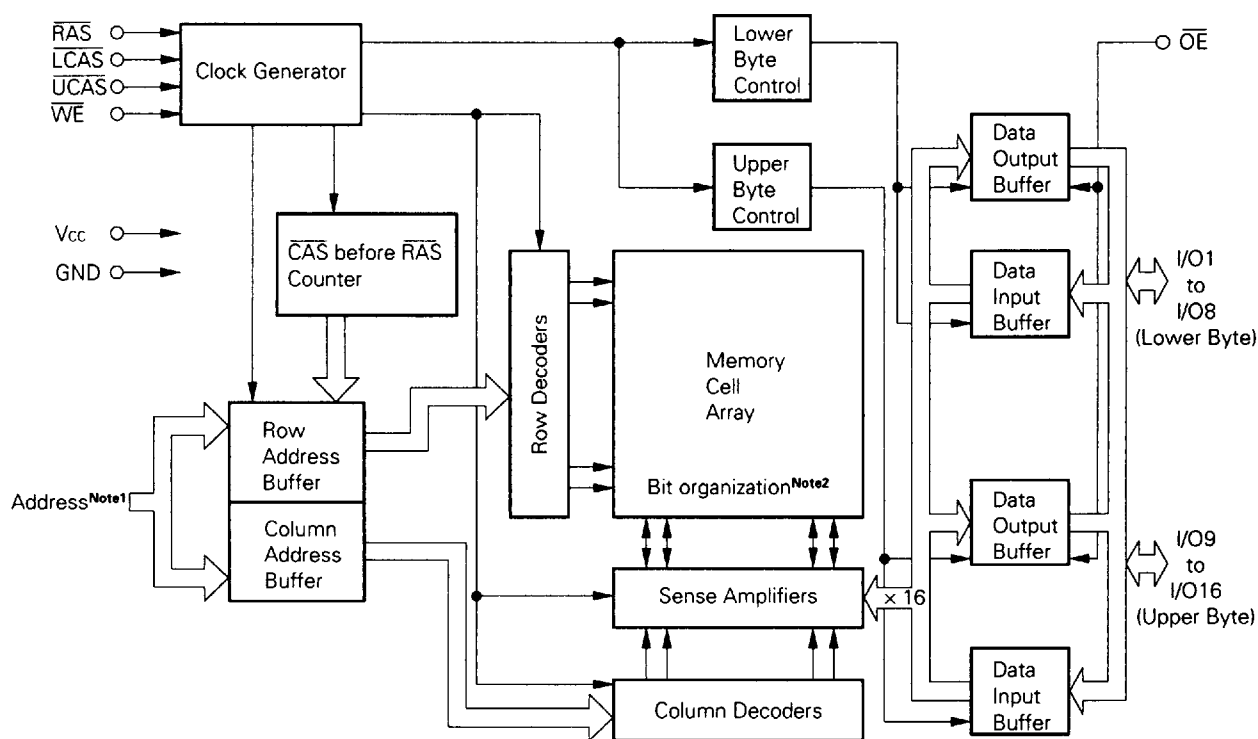
42-pin Plastic SOJ



Notes 1. A11 . . . μPD42S16160L, 4216160L NC . . . μPD42S18160L, 4218160L
2. A10 . . . μPD42S16160L, 4216160L NC . . . μPD42S18160L, 4218160L

A0 to A11 : Address Inputs
I/O1 to I/O16 : Data Inputs/Outputs
RAS : Row Address Strobe
UCAS : Column Address Strobe (upper)
LCAS : Column Address Strobe (lower)
WE : Write Enable
OE : Output Enable
Vcc : Supply Voltage
GND : Ground
NC : No Connection

BLOCK DIAGRAM



Notes 1.

Part number	Row address	Column address
μPD42S16160L, 4216160L	A0 to A11	A0 to A7
μPD42S18160L, 4218160L	A0 to A9	A0 to A9

2. μPD42S16160L, 4216160L ... 4 096 × 256 × 16 μPD42S18160L, 4218160L ... 1 024 × 1 024 × 16

INPUT/OUTPUT PIN FUNCTIONS

The μPD42S16160L, 4216160L, 42S18160L, 4218160L have input pins $\overline{\text{RAS}}$, $\overline{\text{CAS}}$ ^{Note1}, $\overline{\text{WE}}$, $\overline{\text{OE}}$, A0 to A11/A9 ^{Note2} and input/output pins I/O1 to I/O16.

Pin name	Input/ Output	Function
$\overline{\text{RAS}}$ (Row address strobe)	Input	$\overline{\text{RAS}}$ activates the sense amplifier by latching a row address and selecting a corresponding word line. It refreshes memory cell array of one line selected by the row address. It also selects the following function. • $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh.
$\overline{\text{CAS}}$ (Column address strobe)		$\overline{\text{CAS}}$ activates data input/output circuit by latching column address and selecting a digit line connected with the sense amplifier.
A0 to A11/A9 ^{Note2} (Address input)		Address bus. Input total 20-bit of address signal, upper 12/10 ^{Note3} -bit and lower 8/10 ^{Note4} -bit in sequence (address multiplex method). Therefore, one word is selected from 1 048 576-word by 16-bit memory cell array. In actual operation, latch row address by specifying row address and activating $\overline{\text{RAS}}$. Then, switch the address bus to column address and activate $\overline{\text{CAS}}$. Each address is taken into the device when $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ are activated. Therefore, the address input setup time (t_{ASR} , t_{ASC}) and hold time (t_{RAH} , t_{CAH}) are specified for the activation of $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$.
$\overline{\text{WE}}$ (Write enable)		Write control signal. Write operation is executed by activating $\overline{\text{RAS}}$, $\overline{\text{CAS}}$ and $\overline{\text{WE}}$.
$\overline{\text{OE}}$ (Output enable)		Read control signal. Read operation can be executed by activating $\overline{\text{RAS}}$, $\overline{\text{CAS}}$ and $\overline{\text{OE}}$. If $\overline{\text{WE}}$ is activated during read operation, $\overline{\text{OE}}$ is to be ineffective in the device. Therefore, read operation cannot be executed.
I/O1 to I/O16 (Data input/output)	Input/ Output	16-bit data bus. I/O1 to I/O16 are used to input/output data.

Notes 1. $\overline{\text{CAS}}$ means $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}}$.

2. A11 ∙ ∙ ∙ μPD42S16160L, 4216160L A9 ∙ ∙ ∙ μPD42S18160L, 4218160L

3. 12 ∙ ∙ ∙ μPD42S16160L, 4216160L 10 ∙ ∙ ∙ μPD42S18160L, 4218160L

4. 8 ∙ ∙ ∙ μPD42S16160L, 4216160L 10 ∙ ∙ ∙ μPD42S18160L, 4218160L

ELECTRICAL SPECIFICATIONS Notes 1, 2, 3

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Rating	Unit
Voltage on Any Pin Relative to GND	V_T		-0.5 to +4.6	V
Supply Voltage	V_{CC}		-0.5 to +4.6	V
Output Current	I_O		20	mA
Power Dissipation	P_D		1	W
Operating Temperature	T_{opt}		0 to +70	°C
Storage Temperature	T_{stg}		-55 to +125	°C

Remark Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply Voltage	V_{CC}		3.0	3.3	3.6	V
High Level Input Voltage	V_{IH}		2.0		$V_{CC} + 0.3$	V
Low Level Input Voltage	V_{IL}		-0.3		+0.8	V
Ambient Temperature	T_a		0		70	°C

CAPACITANCE ($T_a = +25\text{ °C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit
Input Capacitance	C_{I1}	A0 to A11			5	pF
	C_{I2}	$\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$			7	pF
Data Input/Output Capacitance	$C_{I/O}$	I/O1 to I/O16			7	pF

DC CHARACTERISTICS (Recommended Operating Conditions unless otherwise noted)[μ PD42S16160L, 4216160L]

Parameter		Symbol	Test Condition	MIN.	MAX.	Unit	Notes
Operating current		I _{CC1}	$\overline{\text{RAS}}, \overline{\text{CAS}}$ Cycling $t_{\text{RC}} = t_{\text{RC}}(\text{MIN.}),$ $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 60 \text{ ns}$	90	mA	4, 5, 8
				$t_{\text{RAC}} = 70 \text{ ns}$	80		
				$t_{\text{RAC}} = 80 \text{ ns}$	70		
Standby current	μ PD42S16160L	I _{CC2}	$V_{\text{IH}}(\text{MIN.}) \leq \overline{\text{RAS}}, \overline{\text{CAS}}$	$I_o = 0 \text{ mA}$	0.5	mA	
			$V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{RAS}}, \overline{\text{CAS}}$	$I_o = 0 \text{ mA}$	0.15		
	μ PD4216160L		$V_{\text{IH}}(\text{MIN.}) \leq \overline{\text{RAS}}, \overline{\text{CAS}}$	$I_o = 0 \text{ mA}$	2		
			$V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{RAS}}, \overline{\text{CAS}}$	$I_o = 0 \text{ mA}$	0.5		
RAS only refresh current		I _{CC3}	$\overline{\text{RAS}}$ Cycling, $V_{\text{IH}}(\text{MIN.}) \leq \overline{\text{CAS}}$ $t_{\text{RC}} = t_{\text{RC}}(\text{MIN.}),$ $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 60 \text{ ns}$	90	mA	4,5,6,8
				$t_{\text{RAC}} = 70 \text{ ns}$	80		
				$t_{\text{RAC}} = 80 \text{ ns}$	70		
Operating current (Fast page mode)		I _{CC4}	$\overline{\text{RAS}} \leq V_{\text{IL}}(\text{MAX.})$ $\overline{\text{CAS}}$ Cycling, $t_{\text{PC}} = t_{\text{PC}}(\text{MIN.}),$ $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 60 \text{ ns}$	90	mA	4, 5, 7
				$t_{\text{RAC}} = 70 \text{ ns}$	80		
				$t_{\text{RAC}} = 80 \text{ ns}$	70		
CAS before RAS refresh current		I _{CC5}	$\overline{\text{RAS}}$ Cycling, $t_{\text{RC}} = t_{\text{RC}}(\text{MIN.}),$ $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 60 \text{ ns}$	90	mA	4, 5
				$t_{\text{RAC}} = 70 \text{ ns}$	80		
				$t_{\text{RAC}} = 80 \text{ ns}$	70		
CAS before RAS long refresh current (4 096 cycles/128 ms, only for μ PD42S16160L)		I _{CC6}	Standby : $V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{RAS}}$ CAS before RAS refresh : 4 096 cycles/128 ms $\overline{\text{RAS}}, \overline{\text{CAS}} : 0 \text{ V} \leq V_{\text{IL}} \leq 0.2 \text{ V}$ $V_{\text{CC}} - 0.2 \text{ V} \leq V_{\text{IH}} \leq V_{\text{IH}}(\text{MAX.})$ $\overline{\text{WE}}, \overline{\text{OE}} : V_{\text{IH}}$ Address input : Don't care Output : Open	$t_{\text{RAS}} \leq 1 \mu\text{s}$	220	μA	4, 5
Self refresh current (CAS before RAS self refresh, only for μ PD42S16160L)		I _{CC7}	$I_o = 0 \text{ mA}$ $\overline{\text{RAS}}, \overline{\text{CAS}} : 0 \text{ V} \leq V_{\text{IL}} \leq 0.2 \text{ V}$ $V_{\text{CC}} - 0.2 \text{ V} \leq V_{\text{IH}} \leq V_{\text{IH}}(\text{MAX.})$		150	μA	
Input leakage current		I _{IL(L)}	$V_i = 0 \text{ to } 3.6 \text{ V}$ all other pins not under test = 0 V	-5	+5	μA	
Output leakage current		I _{OL(L)}	Outputs are disabled (Hi-Z) $V_o = 0 \text{ to } 3.6 \text{ V}$	-5	+5	μA	
High level output voltage		V _{OH}	$I_o = -2.0 \text{ mA}$	2.4		V	
Low level output voltage		V _{OL}	$I_o = 2.0 \text{ mA}$		0.4	V	

[μ PD42S18160L, 4218160L]

Parameter		Symbol	Test Condition	MIN.	MAX.	Unit	Notes
Operating current		I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ Cycling $t_{RC} = t_{RC(MIN.)}$, $I_O = 0$ mA	$t_{RAC} = 60$ ns	150	mA	4, 5, 8
				$t_{RAC} = 70$ ns	140		
				$t_{RAC} = 80$ ns	130		
Standby current	μ PD42S18160L	I_{CC2}	$V_{IH(MIN.)} \leq \overline{RAS}$, $\overline{CAS}$ $I_O = 0$ mA		0.5	mA	
			$V_{CC}-0.2$ V $\leq \overline{RAS}$, $\overline{CAS}$ $I_O = 0$ mA		0.15		
	μ PD4218160L		$V_{IH(MIN.)} \leq \overline{RAS}$, $\overline{CAS}$ $I_O = 0$ mA		2		
			$V_{CC}-0.2$ V $\leq \overline{RAS}$, $\overline{CAS}$ $I_O = 0$ mA		0.5		
$\overline{RAS}$ only refresh current		I_{CC3}	$\overline{RAS}$ Cycling, $V_{IH(MIN.)} \leq \overline{CAS}$ $t_{RC} = t_{RC(MIN.)}$, $I_O = 0$ mA	$t_{RAC} = 60$ ns	150	mA	4,5,6,8
				$t_{RAC} = 70$ ns	140		
				$t_{RAC} = 80$ ns	130		
Operating current (Fast page mode)		I_{CC4}	$\overline{RAS} \leq V_{IL(MAX.)}$ $\overline{CAS}$ Cycling, $t_{PC} = t_{PC(MIN.)}$, $I_O = 0$ mA	$t_{RAC} = 60$ ns	90	mA	4, 5, 7
				$t_{RAC} = 70$ ns	80		
				$t_{RAC} = 80$ ns	70		
$\overline{CAS}$ before $\overline{RAS}$ refresh current		I_{CC5}	$\overline{RAS}$ Cycling, $t_{RC} = t_{RC(MIN.)}$, $I_O = 0$ mA	$t_{RAC} = 60$ ns	150	mA	4, 5
				$t_{RAC} = 70$ ns	140		
				$t_{RAC} = 80$ ns	130		
$\overline{CAS}$ before $\overline{RAS}$ long refresh current (1 024 cycles/128 ms, only for μ PD42S18160L)		I_{CC6}	Standby : $V_{CC}-0.2$ V $\leq \overline{RAS}$ $\overline{CAS}$ before $\overline{RAS}$ refresh : 1 024 cycles/128 ms $\overline{RAS}$, $\overline{CAS}$: 0 V $\leq V_{IL} \leq 0.2$ V $V_{CC}-0.2$ V $\leq V_{IH} \leq V_{IH(MAX.)}$ $\overline{WE}$, $\overline{OE}$: V_{IH} Address input : Don't care Output : Open	$t_{RAS} \leq 1$ μ s	180	μ A	4, 5
Self refresh current ($\overline{CAS}$ before $\overline{RAS}$ self refresh, only for μ PD42S18160L)		I_{CC7}	$I_O = 0$ mA $\overline{RAS}$, $\overline{CAS}$: 0 V $\leq V_{IL} \leq 0.2$ V $V_{CC}-0.2$ V $\leq V_{IH} \leq V_{IH(MAX.)}$		150	μ A	
Input leakage current		$I_{I(L)}$	$V_I = 0$ to 3.6 V all other pins not under test = 0 V	-5	+5	μ A	
Output leakage current		$I_{O(L)}$	Outputs are disabled (Hi-Z) $V_O = 0$ to 3.6 V	-5	+5	μ A	
High level output voltage		V_{OH}	$I_O = -2.0$ mA	2.4		V	
Low level output voltage		V_{OL}	$I_O = 2.0$ mA		0.4	V	

★

★

★

AC CHARACTERISTICS

(Recommended Operating Conditions unless otherwise noted) Notes 9, 10

(1/2)

Parameter	Symbol	$t_{RAC} = 60 \text{ ns}$		$t_{RAC} = 70 \text{ ns}$		$t_{RAC} = 80 \text{ ns}$		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read or Write Cycle Time	t_{RC}	110		130		150		ns	
Read Modify Write Cycle Time	t_{RWC}	160		180		200		ns	
Fast Page Mode Cycle Time (Read or Write)	t_{PC}	40		45		50		ns	
Read Modify Write Cycle Time (Fast Page Mode)	t_{PRWC}	85		90		105		ns	
Access Time from $\overline{RAS}$	t_{RAC}		60		70		80	ns	11, 12
Access Time from $\overline{CAS}$ (Falling Edge)	t_{CAC}		15		20		20	ns	11, 12
Access Time from Column Address	t_{AA}		30		35		40	ns	11, 12
Access Time from $\overline{CAS}$ Precharge	t_{ACP}		35		40		45	ns	12
Access Time from $\overline{OE}$	t_{OEA}		15		20		20	ns	12
$\overline{RAS}$ to Column Address Delay Time	t_{RAD}	15	30	15	35	17	40	ns	11
$\overline{CAS}$ to Data Setup Time	t_{CLZ}	0		0		0		ns	12
$\overline{OE}$ to Data Setup Time	t_{OLZ}	0		0		0		ns	12
Output Buffer Turn-off Delay Time ($\overline{CAS}$)	t_{OFF}	0	13	0	15	0	15	ns	13
$\overline{OE}$ to Data Delay Time	t_{OED}	13		15		15		ns	
Output Buffer Turn-off Delay Time ($\overline{OE}$)	t_{OEZ}	0	13	0	15	0	15	ns	13
$\overline{OE}$ Command Hold Time	t_{OEH}	0		0		0		ns	
$\overline{OE}$ to $\overline{RAS}$ inactive Setup Time	t_{OES}	0		0		0		ns	
Transition Time (Rise and Fall)	t_T	3	50	3	50	3	50	ns	
$\overline{RAS}$ Precharge Time	t_{RP}	40		50		60		ns	
$\overline{RAS}$ Pulse Width (Random Read, Write Cycle)	t_{RAS}	60	10 000	70	10 000	80	10 000	ns	
$\overline{RAS}$ Pulse Width (Fast Page Mode)	t_{RASP}	60	125 000	70	125 000	80	125 000	ns	
$\overline{RAS}$ Hold Time	t_{RSH}	15		18		20		ns	
$\overline{CAS}$ Pulse Width	t_{CAS}	15	10 000	20	10 000	20	10 000	ns	
$\overline{CAS}$ Hold Time	t_{CSH}	60		70		80		ns	
$\overline{RAS}$ to $\overline{CAS}$ Delay Time	t_{RCD}	20	45	20	50	25	60	ns	11
$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	t_{CRP}	5		5		5		ns	14
$\overline{CAS}$ Precharge Time	t_{CPN}	10		10		10		ns	
$\overline{CAS}$ Precharge Time (Fast Page Mode)	t_{CP}	10		10		10		ns	
$\overline{RAS}$ Precharge $\overline{CAS}$ Hold Time	t_{RPC}	5		5		5		ns	
$\overline{RAS}$ Hold Time from $\overline{CAS}$ Precharge	t_{RHCP}	35		40		45		ns	
Row Address Setup Time	t_{ASR}	0		0		0		ns	
Row Address Hold Time	t_{RAH}	10		10		12		ns	

(2/2)

Parameter	Symbol	t _{RAC} = 60 ns		t _{RAC} = 70 ns		t _{RAC} = 80 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Column Address Setup Time	t _{ASC}	0		0		0		ns	
Column Address Hold Time	t _{CAH}	15		15		15		ns	
Column Address Lead Time Referenced to $\overline{\text{RAS}}$	t _{RAL}	30		35		40		ns	
Read Command Setup Time	t _{RCS}	0		0		0		ns	
Read Command Hold Time Referenced to $\overline{\text{RAS}}$	t _{RRH}	0		0		0		ns	15
Read Command Hold Time Referenced to $\overline{\text{CAS}}$	t _{RCH}	0		0		0		ns	15
Write Command Hold Time Referenced to $\overline{\text{CAS}}$	t _{WCH}	10		10		15		ns	16
Write Command Pulse Width	t _{WP}	10		10		15		ns	16
Data-in Setup Time	t _{DS}	0		0		0		ns	17
Data-in Hold Time	t _{DH}	10		15		15		ns	17
$\overline{\text{WE}}$ Command Setup Time	t _{WCS}	0		0		0		ns	18
$\overline{\text{CAS}}$ to $\overline{\text{WE}}$ Delay Time	t _{CWD}	38		40		45		ns	18
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ Delay Time	t _{RWD}	83		95		105		ns	18
$\overline{\text{CAS}}$ Precharge Delay Time Referenced to $\overline{\text{WE}}$ (Fast Page Mode)	t _{CPWD}	60		65		70		ns	18
Column Address Delay Time Referenced to $\overline{\text{WE}}$	t _{AWD}	53		60		65		ns	18
Write Command Lead Time Referenced to $\overline{\text{RAS}}$	t _{RWL}	20		20		20		ns	
Write Command Lead Time Referenced to $\overline{\text{CAS}}$	t _{CWL}	15		15		15		ns	
$\overline{\text{CAS}}$ Setup Time for $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Refresh	t _{CSR}	5		5		5		ns	
$\overline{\text{CAS}}$ Hold Time for $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Refresh	t _{CHR}	10		10		10		ns	
$\overline{\text{RAS}}$ Pulse Width ($\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Self Refresh Cycle)	t _{RASS}	100		100		100		μs	19
$\overline{\text{RAS}}$ Precharge Time ($\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Self Refresh Cycle)	t _{RPS}	110		130		150		ns	19
$\overline{\text{CAS}}$ Hold Time ($\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Self Refresh Cycle)	t _{CHS}	-50		-50		-50		ns	19
$\overline{\text{WE}}$ Hold Time	t _{WHR}	15		15		15		ns	
Masked Byte Write Hold Time Referenced to $\overline{\text{RAS}}$	t _{MWH}	0		0		0		ns	
Refresh Time	μPD42S16160L, 42S18160L		128		128		128	ms	19
	μPD4216160L		64		64		64		
	μPD4218160L		16		16		16		

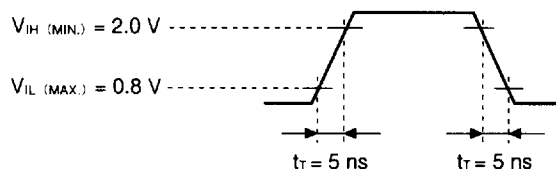
★

★

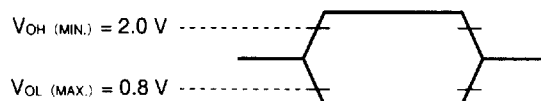
Notes

1. $\overline{\text{CAS}}$ means $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}}$.
2. All voltages are referenced to GND.
3. After power up, wait more than 100 μ s ($\overline{\text{RAS}}$, $\overline{\text{CAS}}$ inactive) and then, execute eight $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ or $\overline{\text{RAS}}$ only refresh cycles as dummy cycles to initialize internal circuit.
4. Icc1 , Icc3 , Icc4 , Icc5 and Icc6 depend on cycle rates (trc and tpc).
5. Specified values are obtained with outputs unloaded.
6. Icc3 is measured assuming that all column address inputs are held at either high or low.
7. Icc4 is measured assuming that all column address inputs are switched only once during each fast page cycle.
8. Icc1 and Icc3 are measured assuming that address can be changed once or less during $\overline{\text{RAS}} \leq V_{\text{IL}}(\text{MAX.})$ and $\overline{\text{CAS}} \geq V_{\text{IH}}(\text{MIN.})$.
9. AC measurements assume $\text{tr} = 5$ ns.
10. AC Characteristics test condition

(1) Input timing specification



(2) Output timing specification



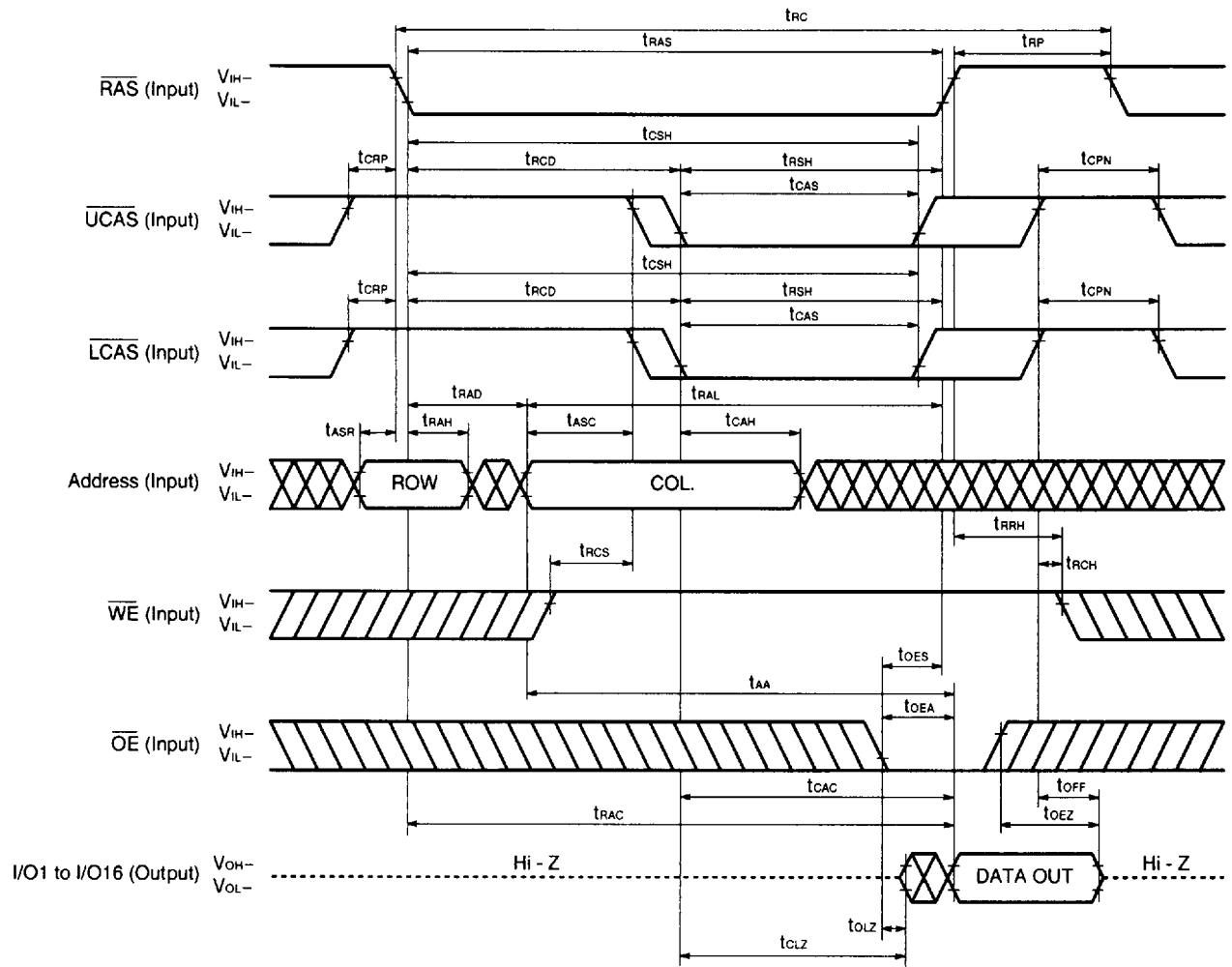
11. For read cycles, access time is defined as follows :

Input Conditions	Access Time	Access Time from $\overline{\text{RAS}}$
$\text{trAD} \leq \text{trAD}(\text{MAX.})$, $\text{trCD} \leq \text{trCD}(\text{MAX.})$	$\text{trAC}(\text{MAX.})$	$\text{trAC}(\text{MAX.})$
$\text{trAD} > \text{trAD}(\text{MAX.})$, $\text{trCD} \leq \text{trCD}(\text{MAX.})$	$\text{tAA}(\text{MAX.})$	$\text{trAD} + \text{tAA}(\text{MAX.})$
$\text{trCD} > \text{trCD}(\text{MAX.})$	$\text{tCAC}(\text{MAX.})$	$\text{trCD} + \text{tCAC}(\text{MAX.})$

$\text{trAD}(\text{MAX.})$ and $\text{trCD}(\text{MAX.})$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time (trAC , tAA or tCAC) is to be used for finding out when output data will be available. Therefore, the input conditions $\text{trAD} \geq \text{trAD}(\text{MAX.})$ and $\text{trCD} \geq \text{trCD}(\text{MAX.})$ will not cause any operation problems.

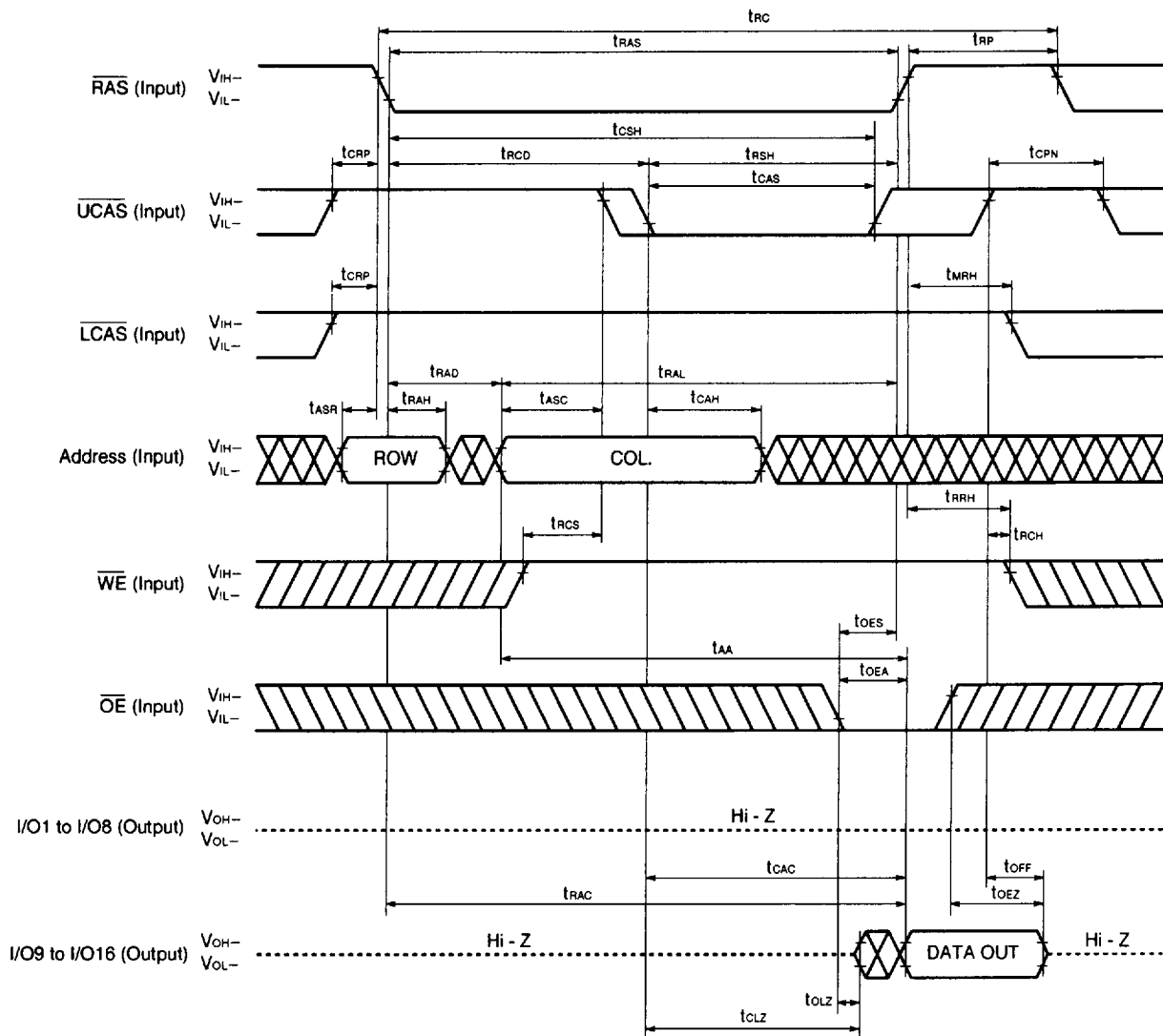
12. Loading conditions are 1TTL and 100 pF.
13. $\text{tOFF}(\text{MAX.})$ and $\text{tOEZ}(\text{MAX.})$ define the time at which the output achieves the condition of Hi-Z and are not referenced to V_{OH} or V_{OL} .
14. $\text{tCRP}(\text{MIN.})$ requirement should be applied for $\overline{\text{RAS}}/\overline{\text{CAS}}$ cycles preceded by any cycles.
15. Either $\text{trCH}(\text{MIN.})$ or $\text{trRH}(\text{MIN.})$ should be met in read cycles.
16. $\text{tWP}(\text{MIN.})$ is applied for late write cycles or read modify write cycles. In early write cycles, $\text{twCH}(\text{MIN.})$ should be met.
17. $\text{tDS}(\text{MIN.})$ and $\text{tDH}(\text{MIN.})$ are referenced to the $\overline{\text{CAS}}$ falling edge in early write cycles. In late write cycles and read modify write cycles, they are referenced to the $\overline{\text{WE}}$ falling edge.
18. If $\text{twCS} \geq \text{twCS}(\text{MIN.})$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle. If $\text{trWD} \geq \text{trWD}(\text{MIN.})$, $\text{tcWD} \geq \text{tcWD}(\text{MIN.})$, $\text{tAWD} \geq \text{tAWD}(\text{MIN.})$ and $\text{tcpWD} \geq \text{tcpWD}(\text{MIN.})$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.
19. This specification is applied only for the μ PD42S16160L, 42S18160L.

READ CYCLE

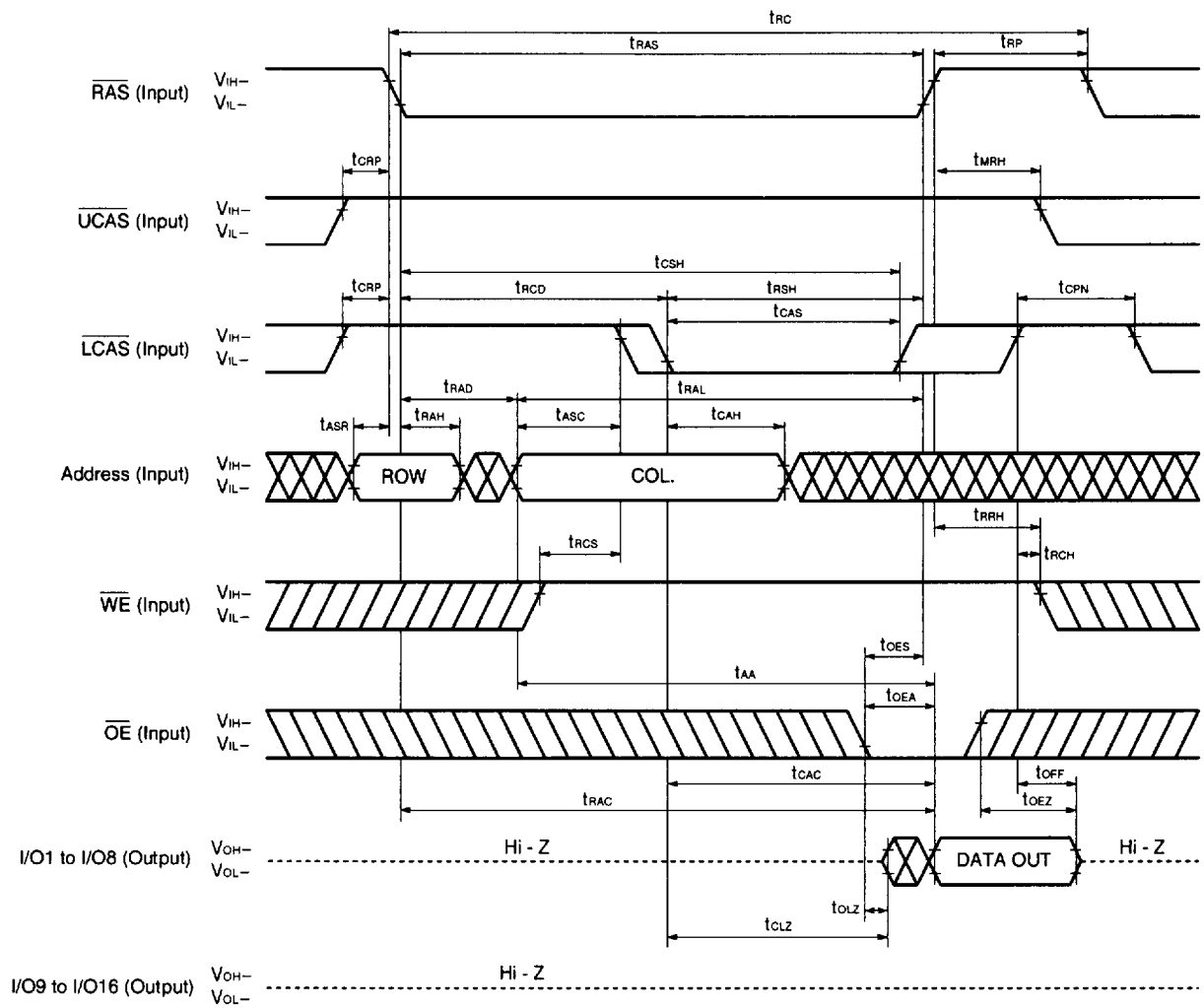


60

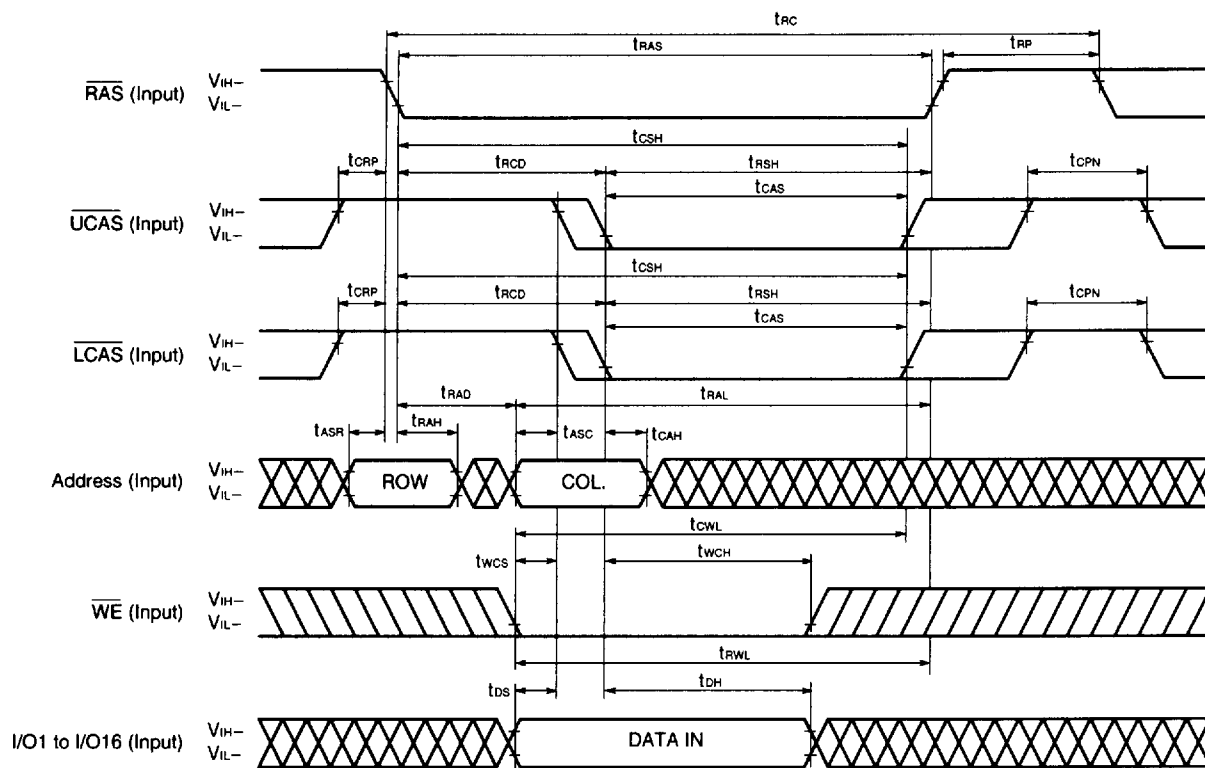
UPPER BYTE READ CYCLE



LOWER BYTE READ CYCLE

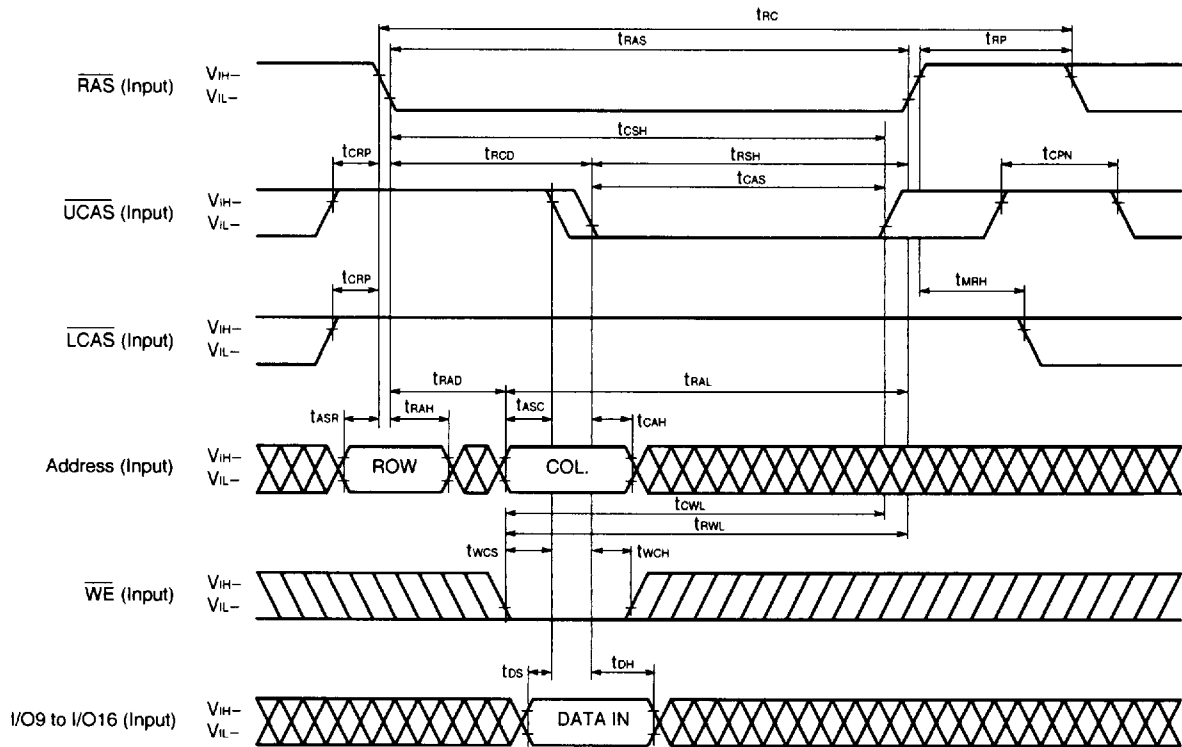


EARLY WRITE CYCLE



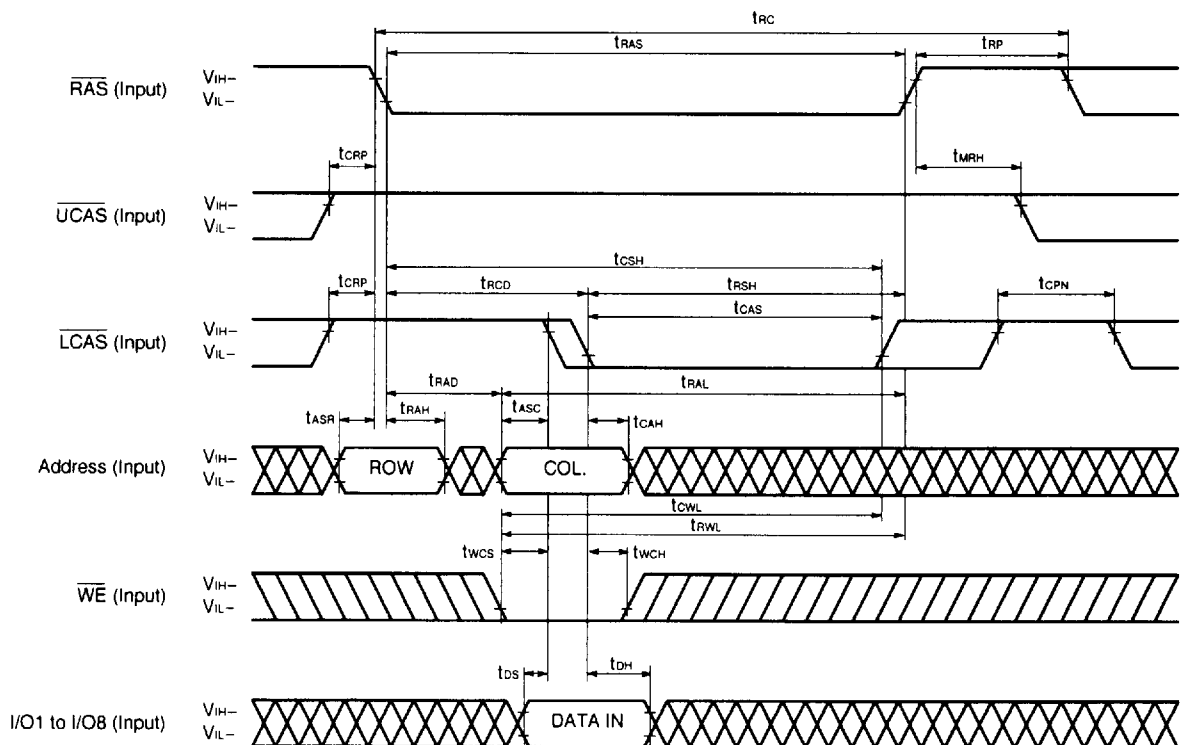
Remark $\overline{OE}$ = Don't care

UPPER BYTE EARLY WRITE CYCLE



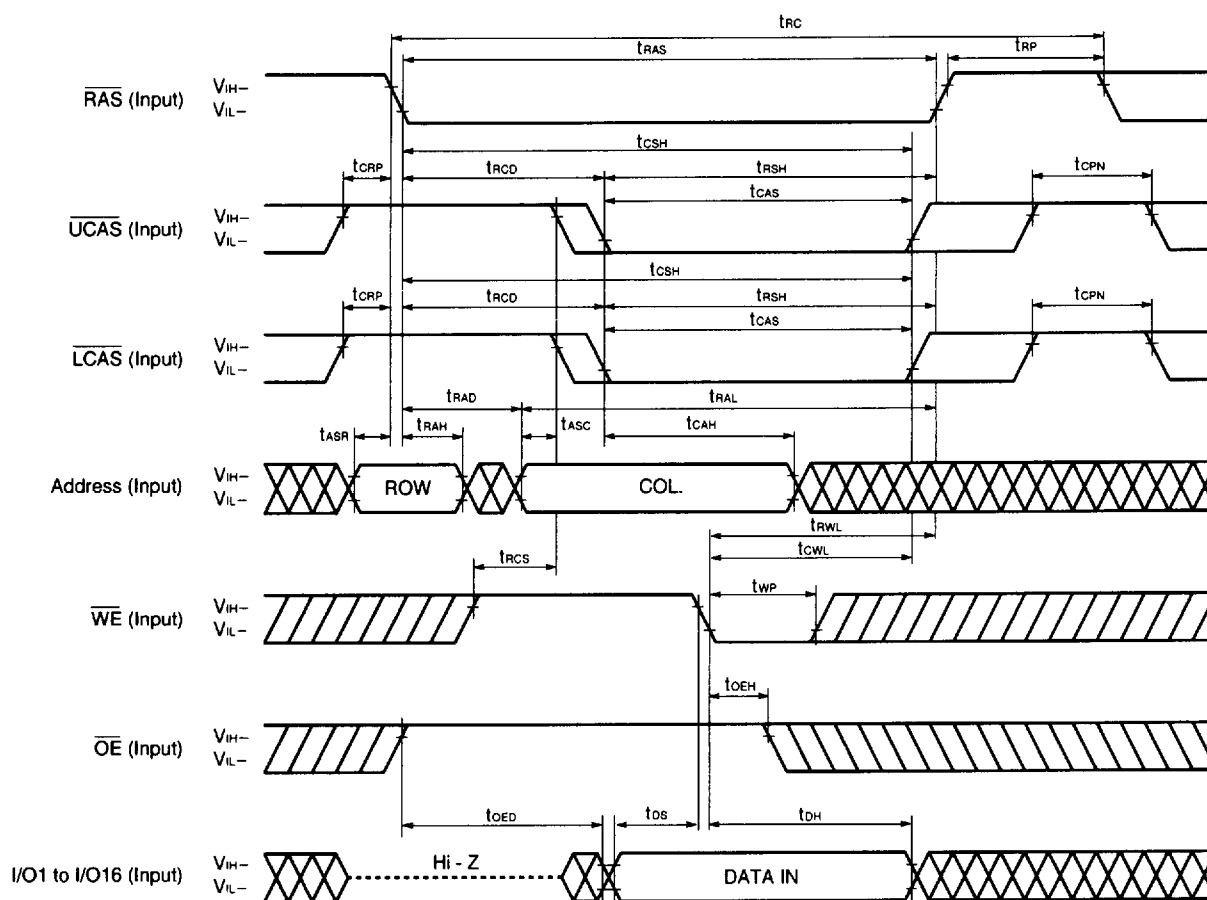
Remark $\overline{OE}$, I/O1 to I/O8 = Don't care

LOWER BYTE EARLY WRITE CYCLE

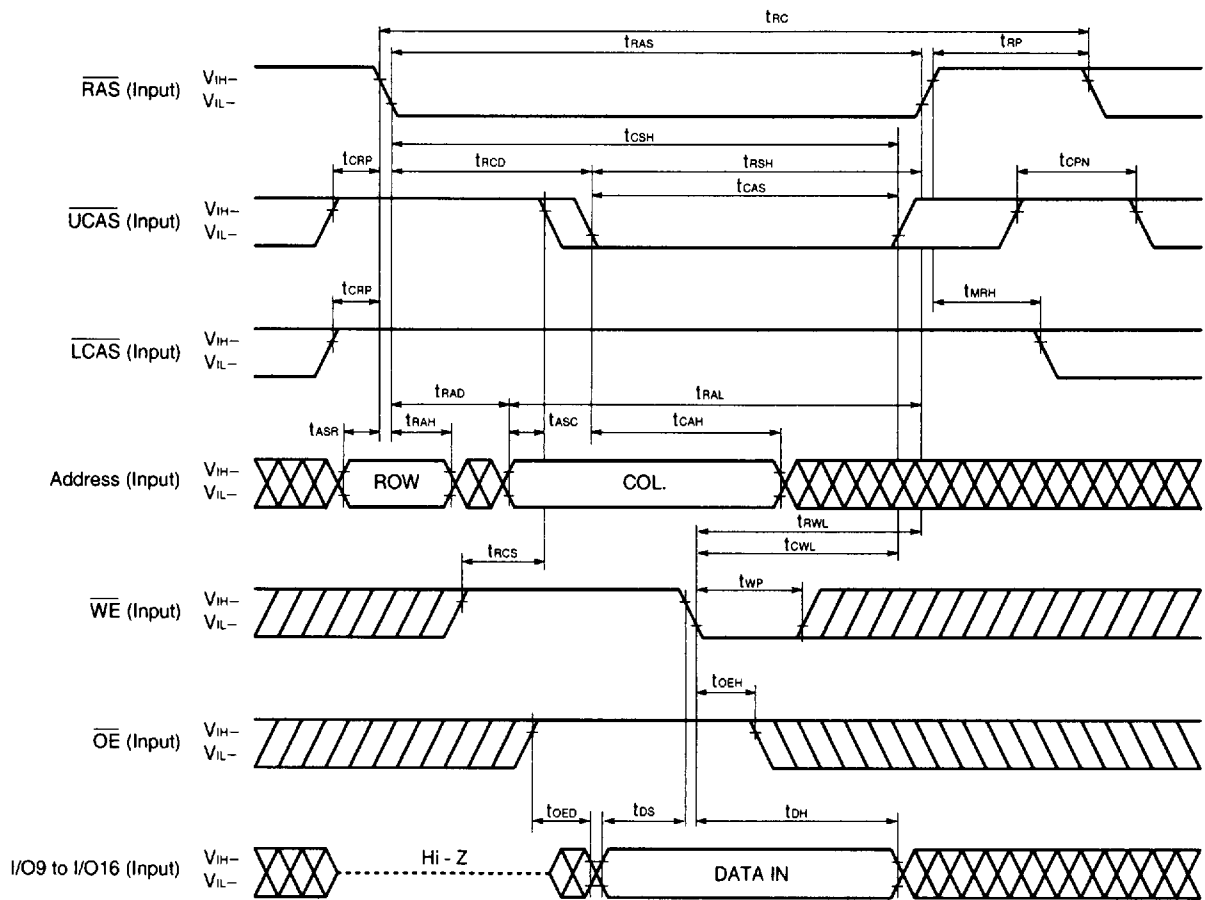


Remark $\overline{OE}$, I/O9 to I/O16 = Don't care

LATE WRITE CYCLE

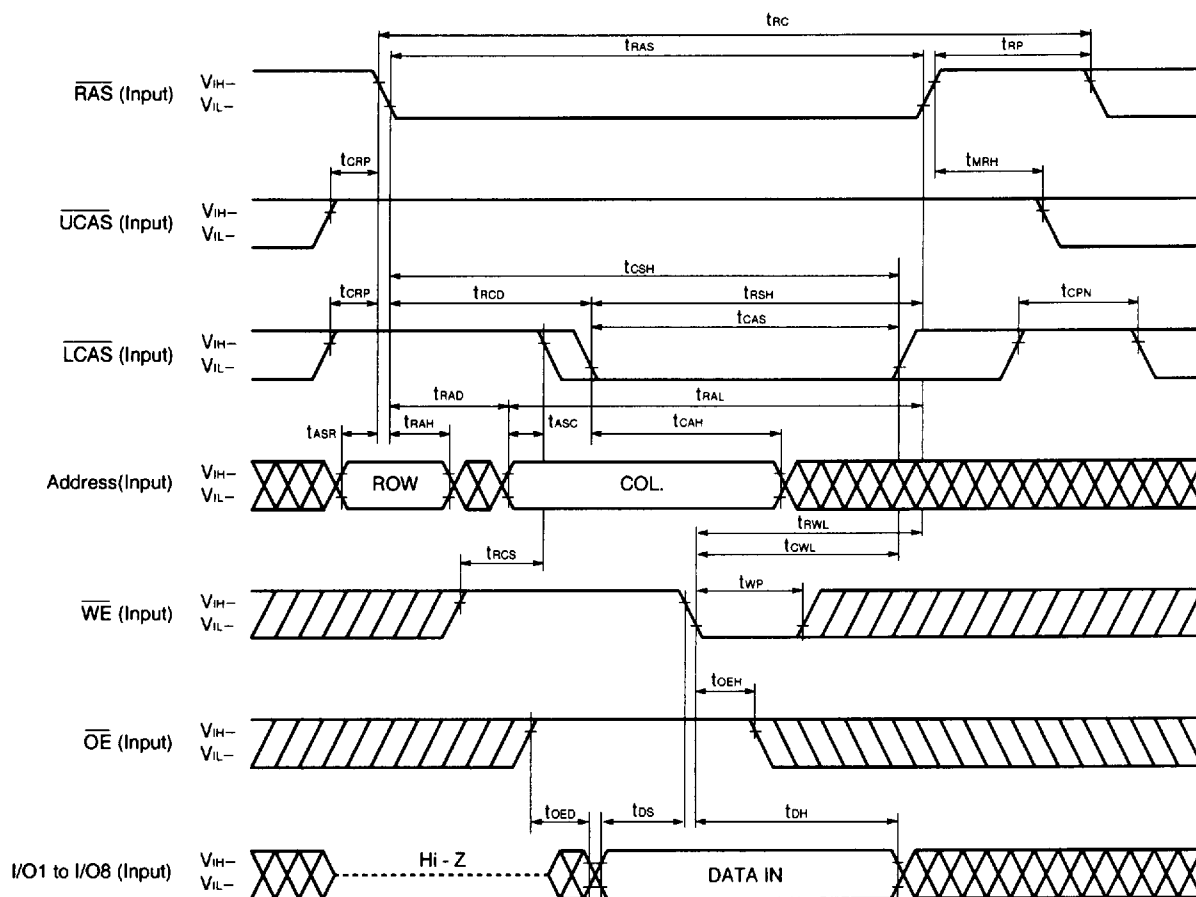


UPPER BYTE LATE WRITE CYCLE



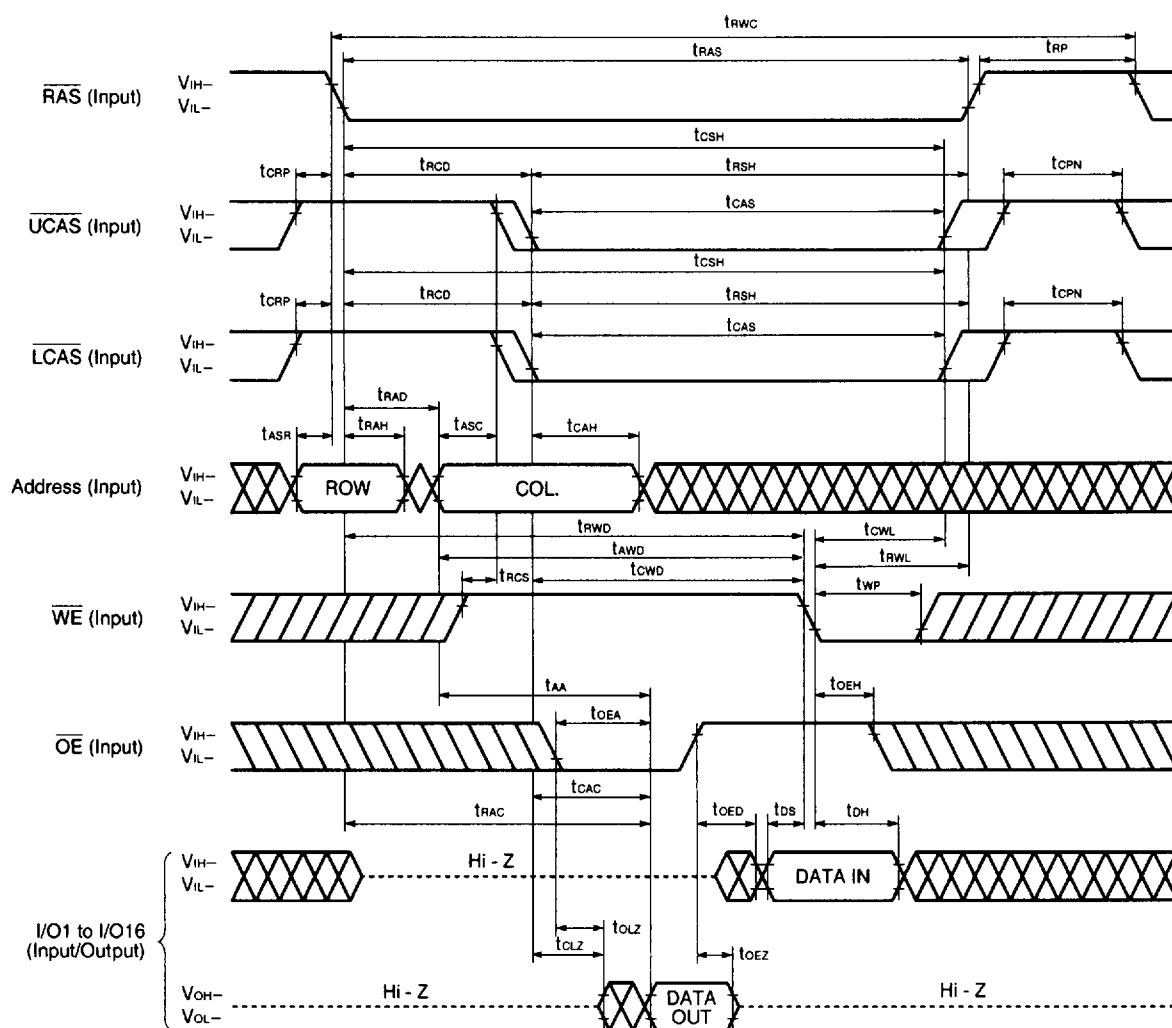
Remark I/O1 to I/O8 = Don't care

LOWER BYTE LATE WRITE CYCLE

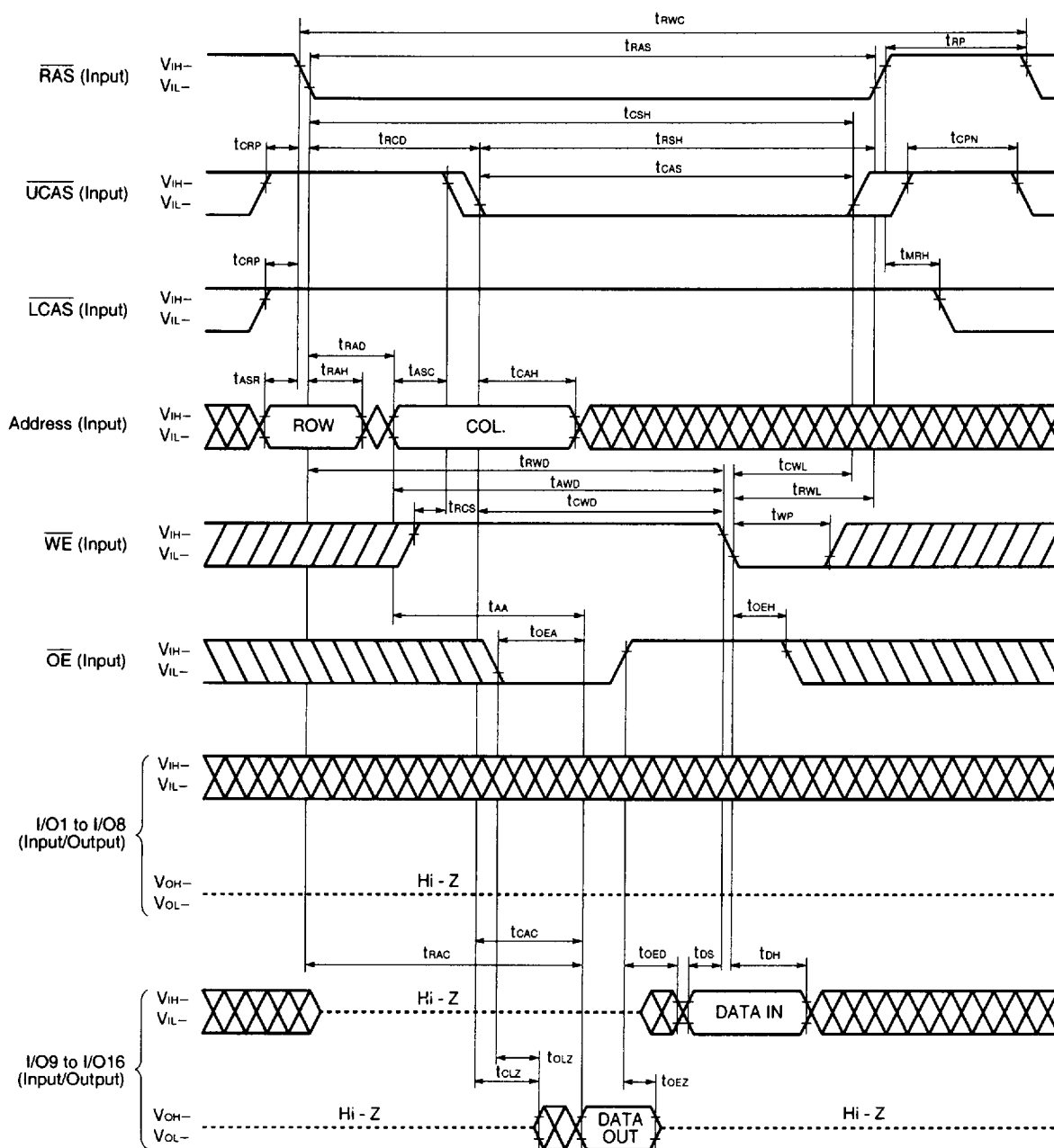


Remark I/O9 to I/O16 = Don't care

★



★ UPPER BYTE READ MODIFY WRITE CYCLE



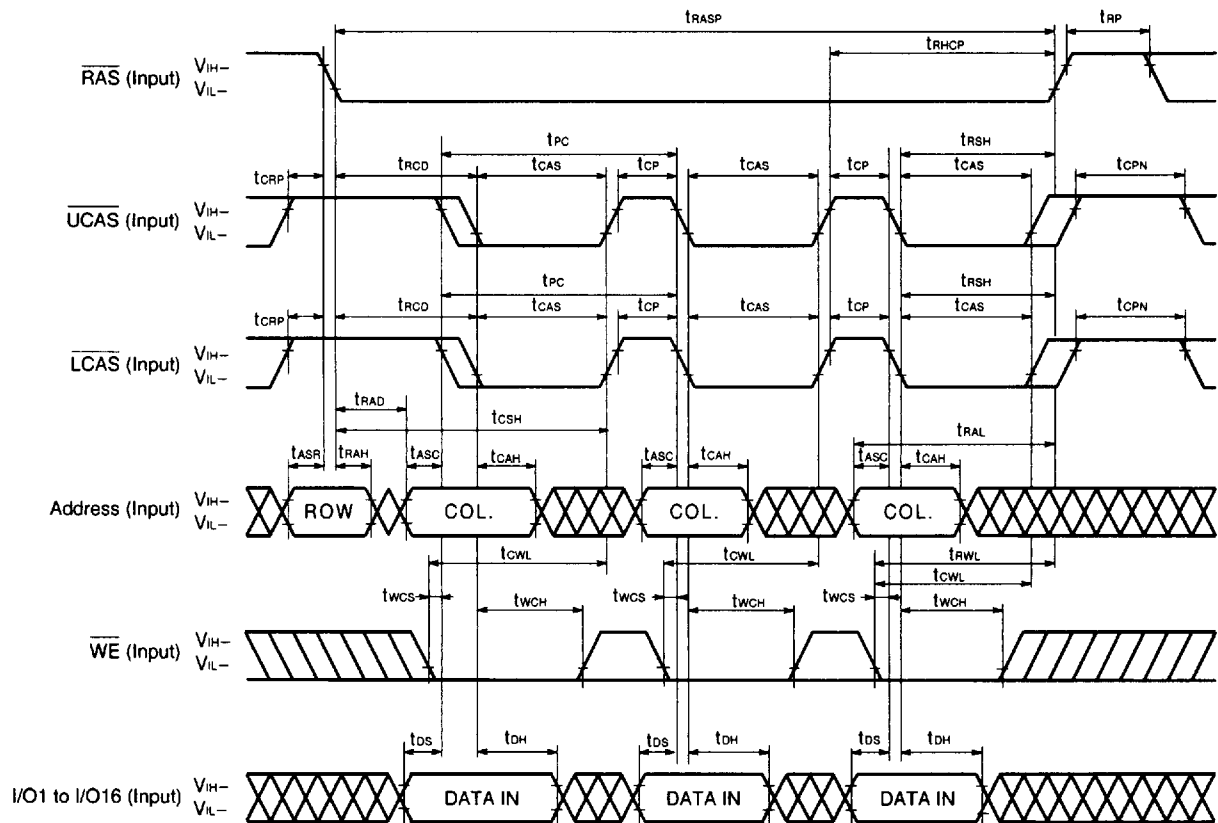
★



72

Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{\text{CAS}}$ cycles within the same $\overline{\text{RAS}}$ cycle.

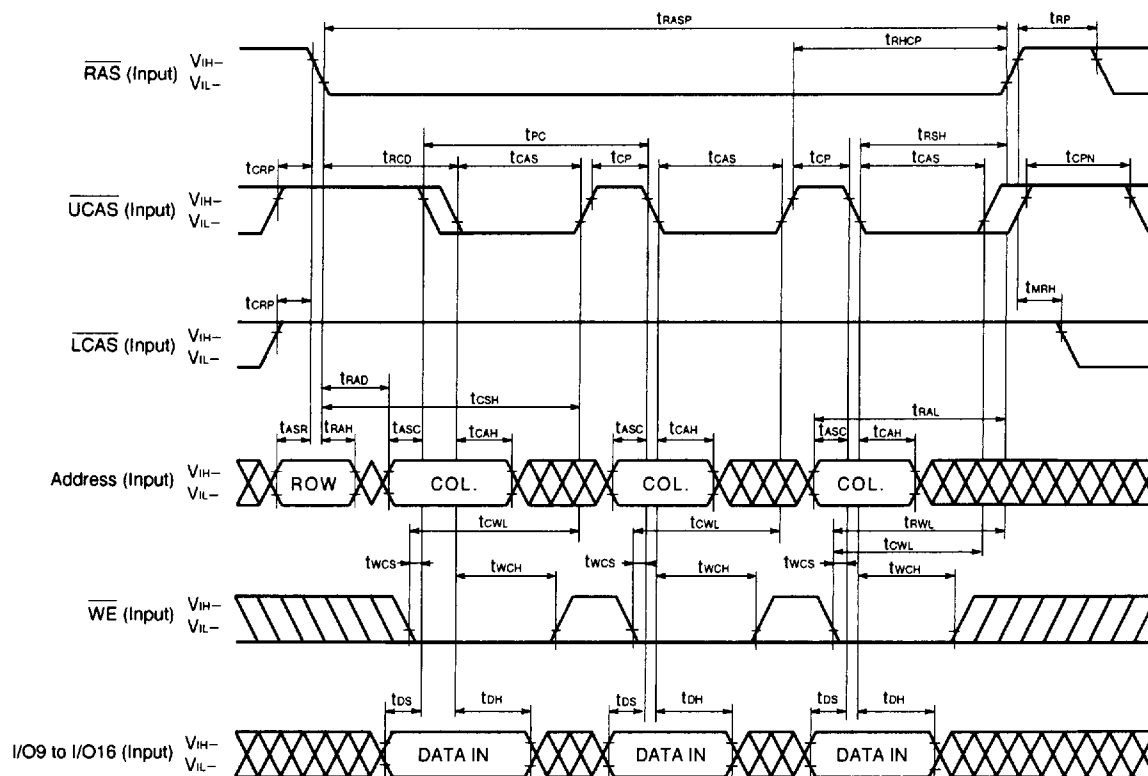
FAST PAGE MODE EARLY WRITE CYCLE



Remark $\overline{OE} = \text{Don't care}$

In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

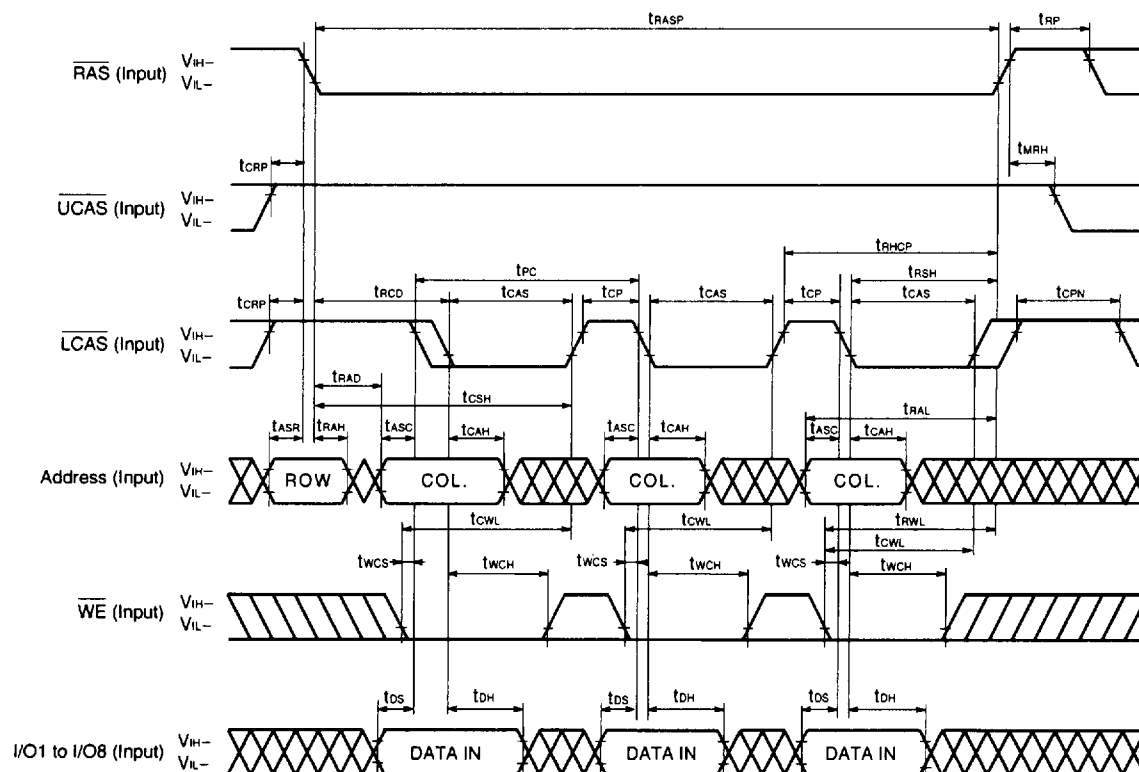
FAST PAGE MODE UPPER BYTE EARLY WRITE CYCLE



Remark I/O1 to I/O8, $\overline{\text{OE}}$ = Don't care

In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{\text{CAS}}$ cycles within the same $\overline{\text{RAS}}$ cycle.

FAST PAGE MODE LOWER BYTE EARLY WRITE CYCLE



Remark I/O9 to I/O16, $\overline{\text{OE}}$ = Don't care

In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{\text{CAS}}$ cycles within the same $\overline{\text{RAS}}$ cycle.

6427525 0052210 324

The diagram illustrates the timing relationships between several control and data signals during memory access operations. The signals shown are:

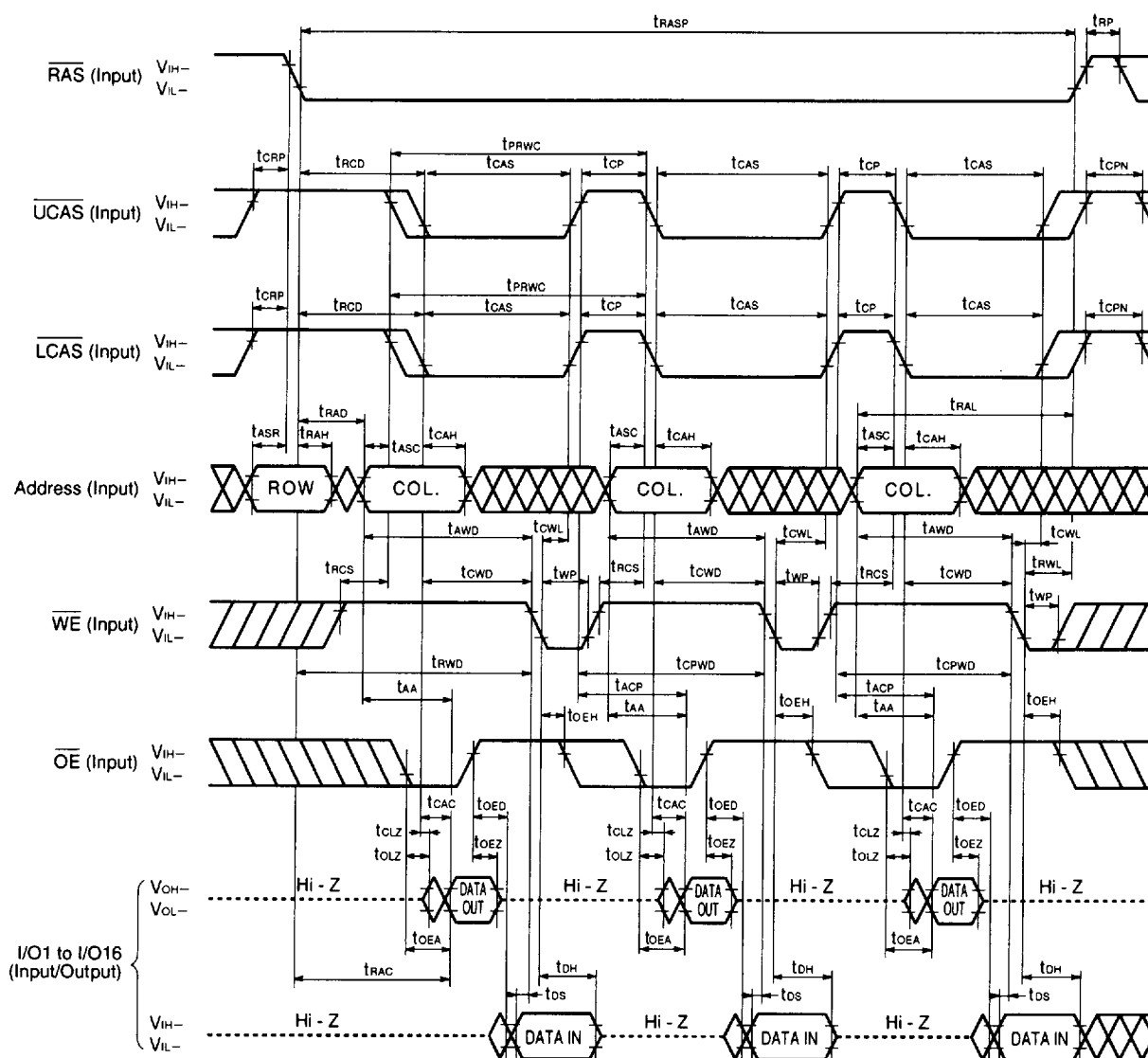
- RAS (Input)**: Row Address Strobe. Timing parameters include t_{CSH} , t_{RASP} , t_{RHCP} , and t_{RP} .
- UCAS (Input)**: Column Address Strobe. Timing parameters include t_{CRP} , t_{RCD} , t_{CAS} , t_{CP} , t_{ASH} , t_{CPN} , and t_{MRH} .
- LCAS (Input)**: Local Column Address Strobe. Timing parameter includes t_{RAD} .
- Address (Input)**: Shows three cycles labeled ROW, COL., and COL. with parameters t_{ASR} , t_{RAH} , t_{ASC} , t_{CAH} , and t_{RAL} .
- WE (Input)**: Write Enable. Timing parameters include t_{RGS} , t_{WPL} , and t_{RWL} .
- OE (Input)**: Output Enable. Timing parameters include t_{OEH} .
- I/O9 to I/O16 (Input)**: Data bus input/output. Timing parameters include t_{DS} , t_{DH} , and t_{DZ} . The signal is shown as Hi-Z during certain periods.

In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

[illegible]

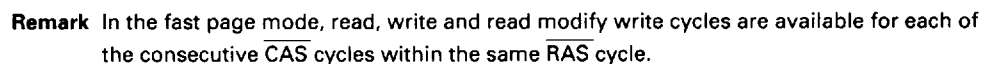
In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

★ FAST PAGE MODE READ MODIFY WRITE CYCLE

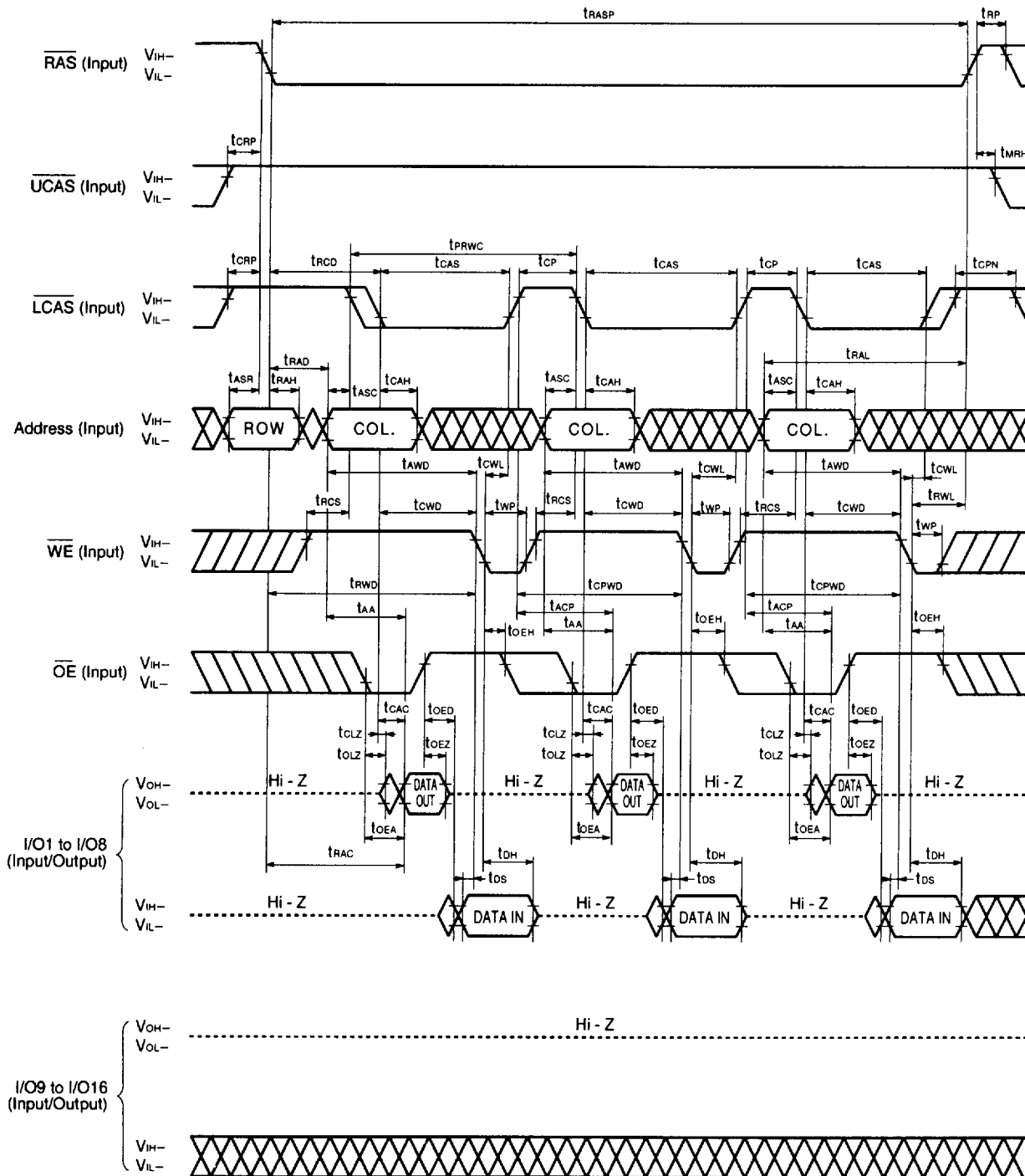


Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

★

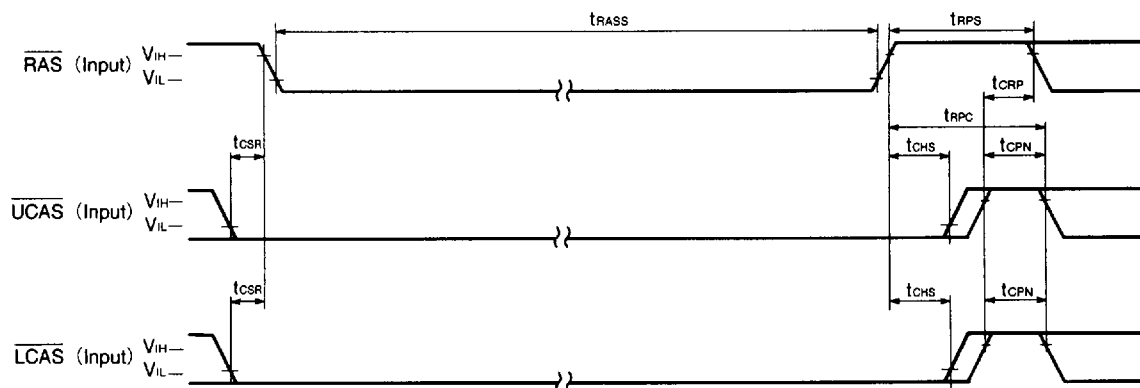


★ FAST PAGE MODE LOWER BYTE READ MODIFY WRITE CYCLE



Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{\text{CAS}}$ cycles within the same $\overline{\text{RAS}}$ cycle.

CAS BEFORE RAS SELF REFRESH CYCLE (Only for the μ PD42S16160L, 42S18160L)



Remark Address, $\overline{WE}$, $\overline{OE}$ = Don't care I/O1 to I/O16 = Hi - Z

How to use CAS before RAS self refresh mode

CAS before RAS self refresh mode can't be used by itself. It must be used with performing one of 3 refreshes below.

• **When using distributed CAS before RAS refresh**

Refresh 4 096 times (μ PD42S16160L) or 1 024 times (μ PD42S18160L) during 128 ms before set into the CAS before RAS self refresh mode and after reset. ★

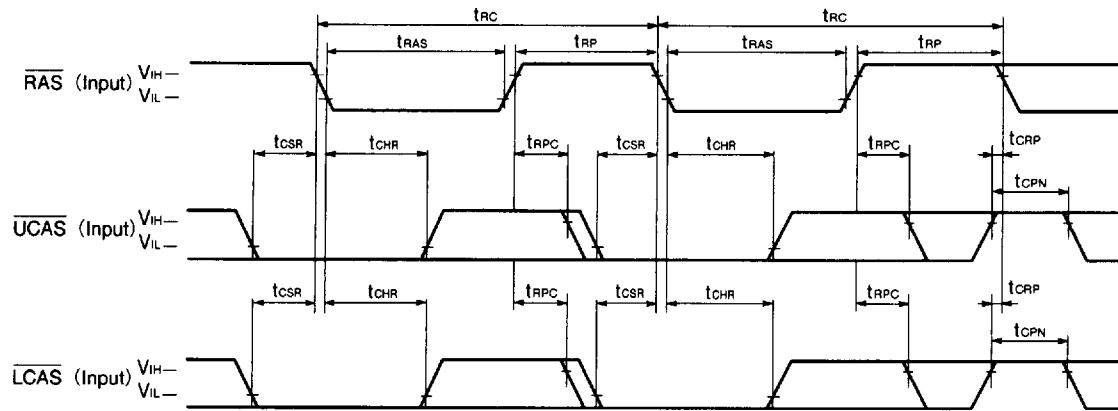
• **When using burst CAS before RAS refresh**

Refresh 4 096 times during 64 ms (μ PD42S16160L) or 1 024 times during 16 ms (μ PD42S18160L) before set into the CAS before RAS self refresh mode and after reset.

• **When using RAS only refresh**

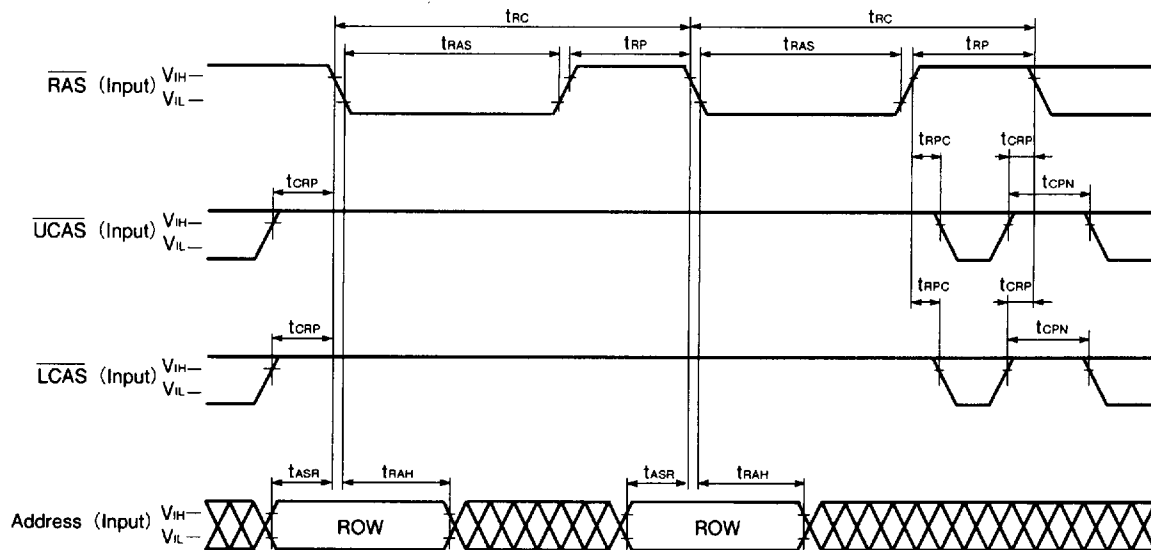
Refresh all refresh addresses during 64 ms (μ PD42S16160L) or 16 ms (μ PD42S18160L) before set into the CAS before RAS self refresh mode and after reset.

CAS BEFORE RAS REFRESH CYCLE



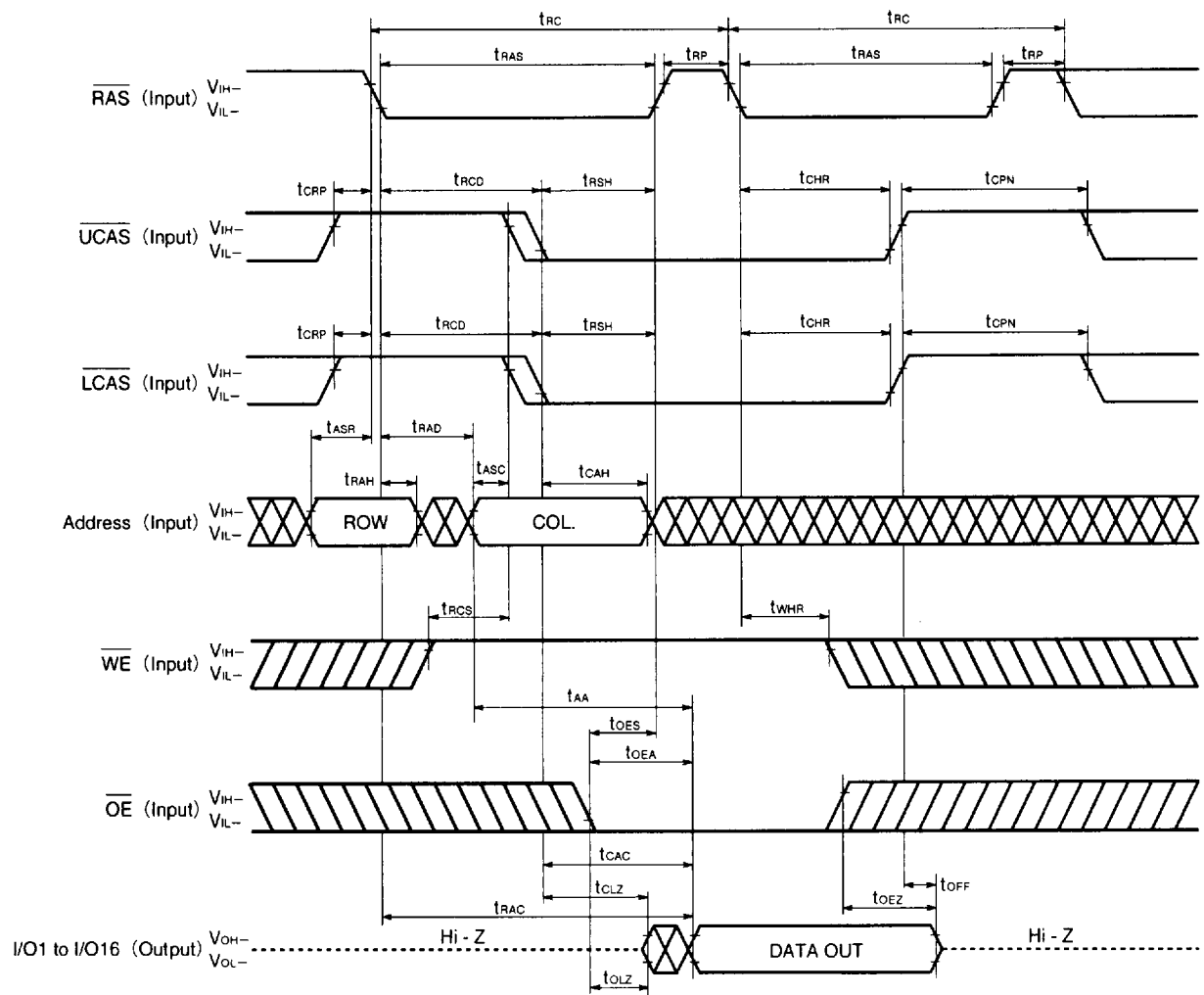
Remark Address, $\overline{WE}$, $\overline{OE}$ = Don't care I/O1 to I/O16 = Hi - Z

RAS ONLY REFRESH CYCLE

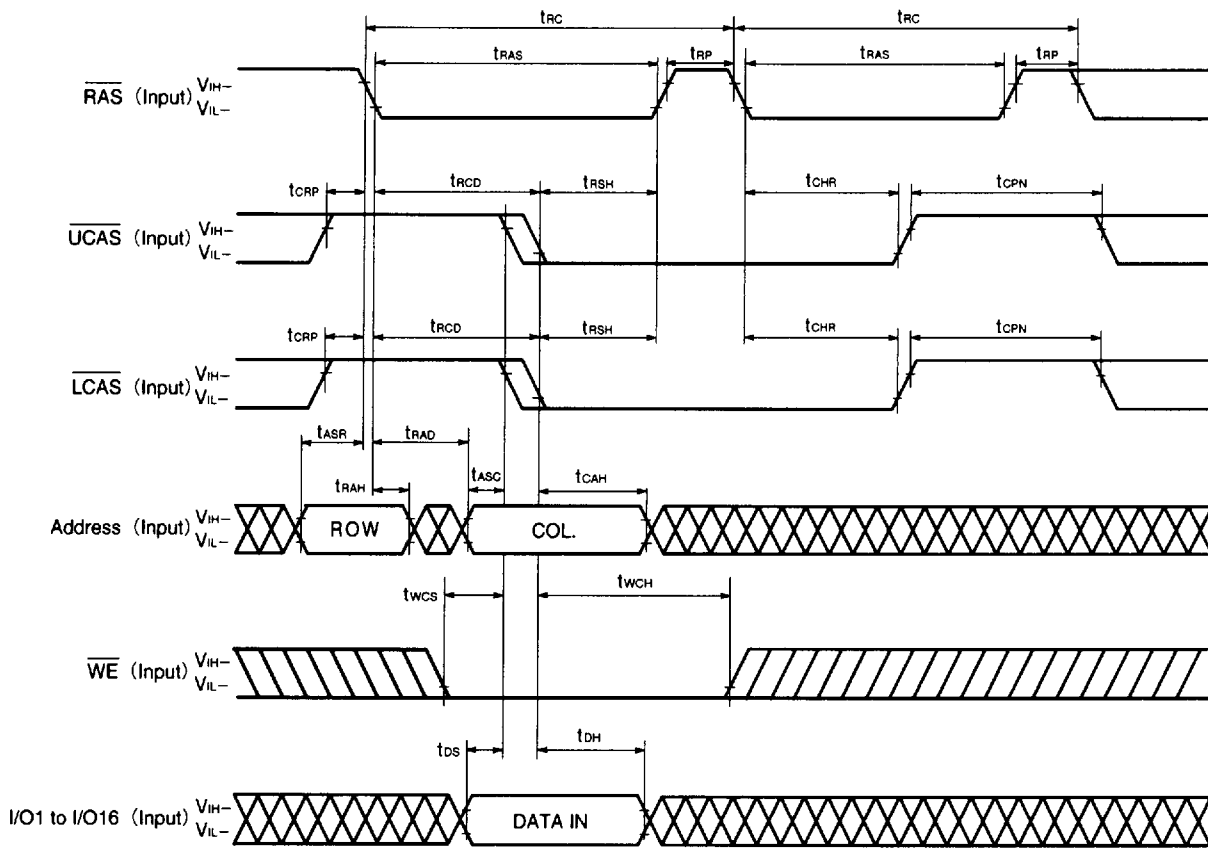


Remark $\overline{WE}$, $\overline{OE}$ = Don't care I/O1 to I/O16 = Hi - Z

HIDDEN REFRESH CYCLE (READ)

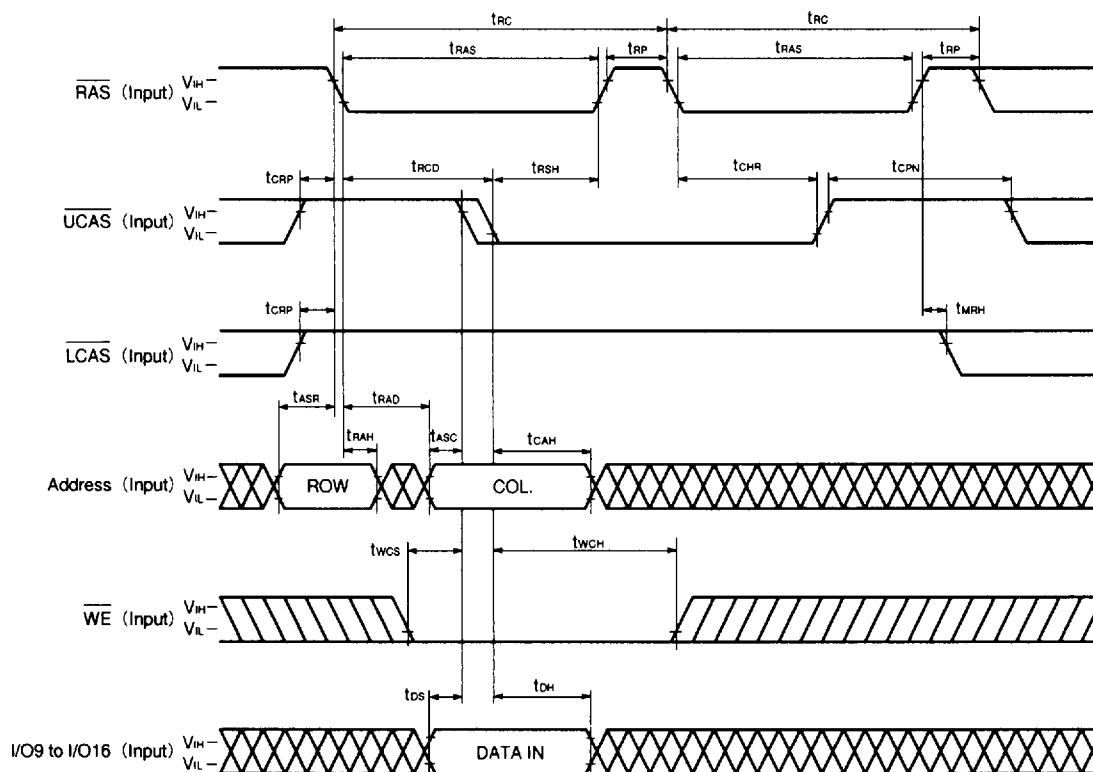


HIDDEN REFRESH CYCLE (WRITE)



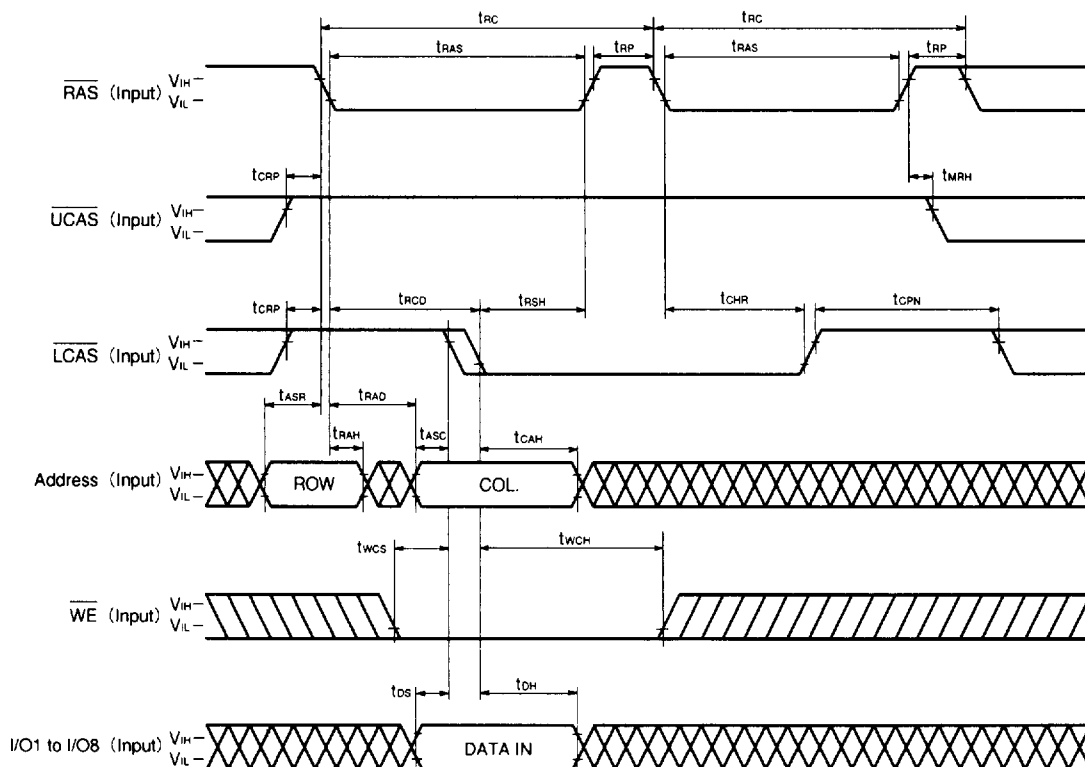
Remark $\overline{\text{OE}}$ = Don't care

HIDDEN REFRESH CYCLE (UPPER BYTE WRITE)



Remark $\overline{OE}$, I/O1 to I/O8 = Don't care

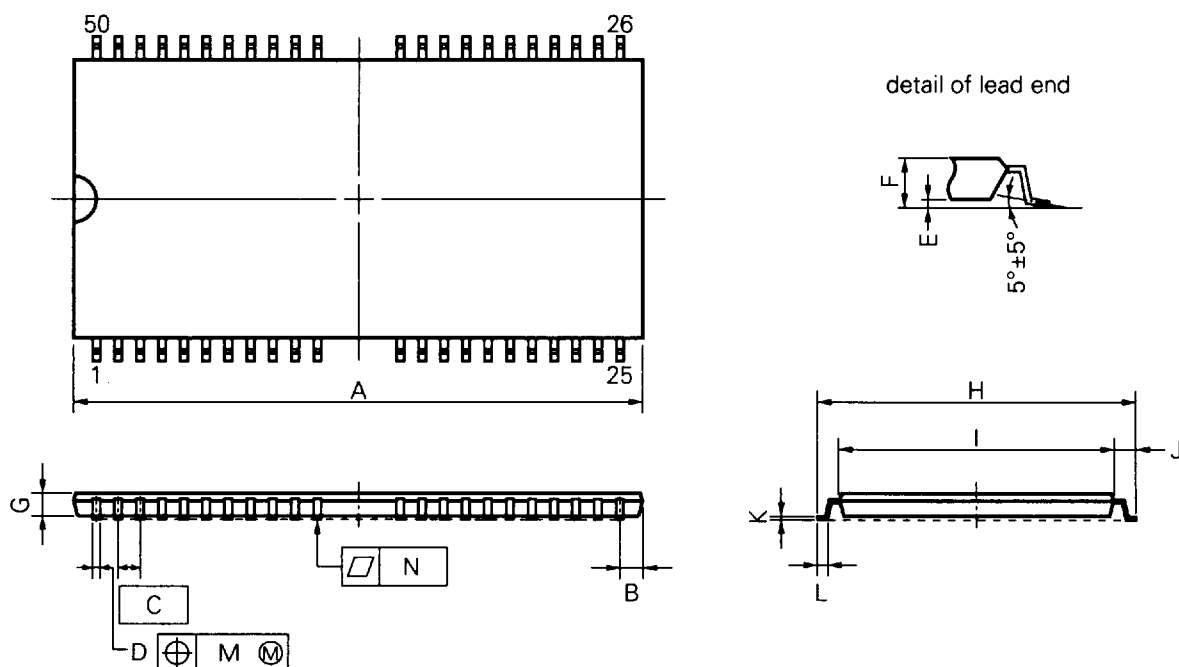
HIDDEN REFRESH CYCLE (LOWER BYTE WRITE)



Remark $\overline{OE}$, I/O9 to I/O16 = Don't care

PACKAGE DRAWINGS

★ 50 PIN PLASTIC TSOP(II) (400 mil)



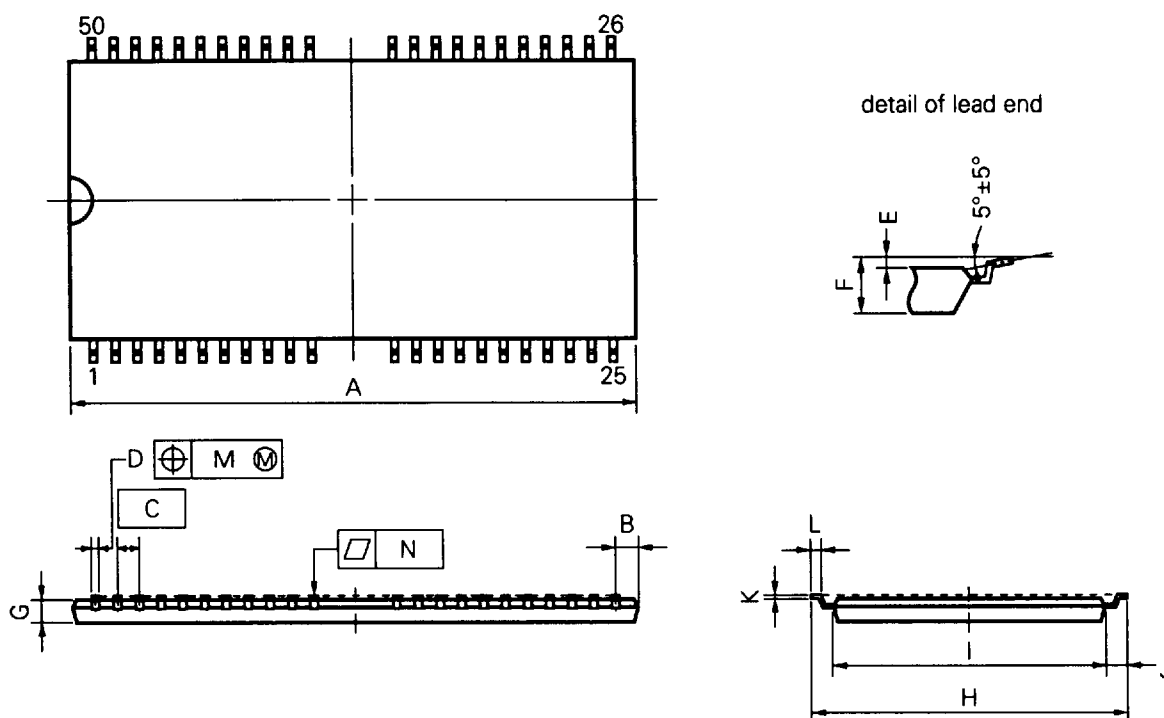
NOTE

Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

S50G5-80-7JF-1

ITEM	MILLIMETERS	INCHES
A	21.45 MAX.	0.845 MAX.
B	1.13 MAX.	0.045 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.30±0.10	0.012 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.13	0.005
N	0.10	0.004

50 PIN PLASTIC TSOP(III) (400 mil)



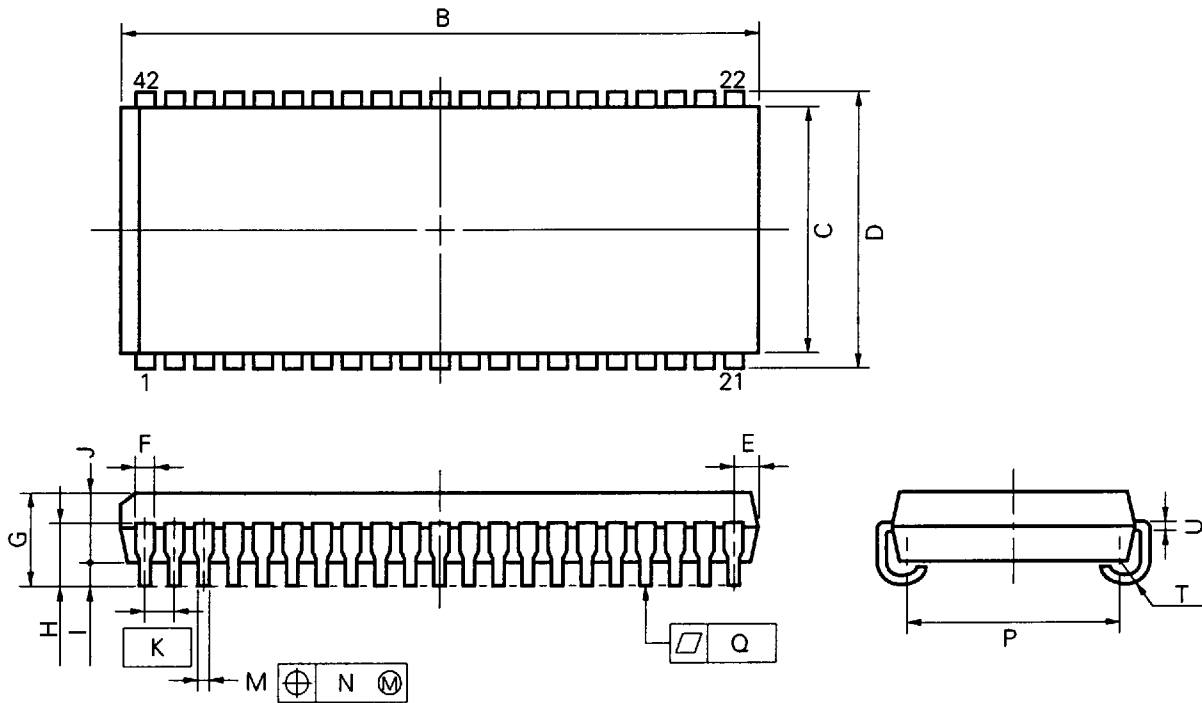
NOTE

Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

S50G5-80-7KF-1

ITEM	MILLIMETERS	INCHES
A	21.45 MAX.	0.845 MAX.
B	1.13 MAX.	0.045 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.30±0.10	0.012 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.13	0.005
N	0.10	0.004

42 PIN PLASTIC SOJ (400 mil)



NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

P42LE-400A

ITEM	MILLIMETERS	INCHES
B	27.56 ^{+0.2} _{-0.35}	1.085 ^{+0.008} _{-0.014}
C	10.16	0.400
D	11.18±0.2	0.440±0.008
E	1.08±0.15	0.043 ^{+0.006} _{-0.007}
F	0.74	0.029
G	3.5±0.2	0.138±0.008
H	2.545±0.2	0.100±0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	0.016 ^{+0.004} _{-0.005}
N	0.12	0.005
P	9.4±0.20	0.370±0.008
Q	0.10	0.004
T	R 0.85	R 0.033
U	0.20 ^{+0.10} _{-0.05}	0.008 ^{+0.004} _{-0.002}

RECOMMENDED SOLDERING CONDITIONS

Please consult with our sales offices for soldering conditions of the μ PD42S16160L, 4216160L, 42S18160L, 4218160L.

TYPE OF SURFACE MOUNT DEVICE

μ PD42S16160LG5, 4216160LG5, 42S18160LG5, 4218160LG5 : 50-pin Plastic TSOP (II) (400 mil)

μ PD42S16160LLE, 4216160LLE, 42S18160LLE, 4218160LLE : 42-pin Plastic SOJ (400 mil)

3. PACKAGE DRAWINGS

26 PIN PLASTIC SOJ (300mil)	24 Leads	495
28 PIN PLASTIC SOJ (400mil)	24 Leads	496
28 PIN PLASTIC SOJ (400mil)	28 Leads	497
32 PIN PLASTIC SOJ (400mil)		498
42 PIN PLASTIC SOJ (400mil)		499
26 PIN PLASTIC TSOP (300mil) *	24 Leads	500
26 PIN PLASTIC TSOP (300mil) *	24 Leads Reverse bent	501
28 PIN PLASTIC TSOP (400mil)	24 Leads	502
28 PIN PLASTIC TSOP (400mil)	24 Leads Reverse bent	503
28 PIN PLASTIC TSOP (400mil)	28 Leads	504
28 PIN PLASTIC TSOP (400mil)	28 Leads Reverse bent	505
32 PIN PLASTIC TSOP (400mil)		506
32 PIN PLASTIC TSOP (400mil)	Reverse bent	507
50 PIN PLASTIC TSOP (400mil)	44 Leads	508
50 PIN PLASTIC TSOP (400mil)	44 Leads Reverse bent	509
24 PIN PLASTIC ZIP (475mil)		510
28 PIN PLASTIC ZIP (475mil)		511
32 PIN PLASTIC ZIP (475mil)		512

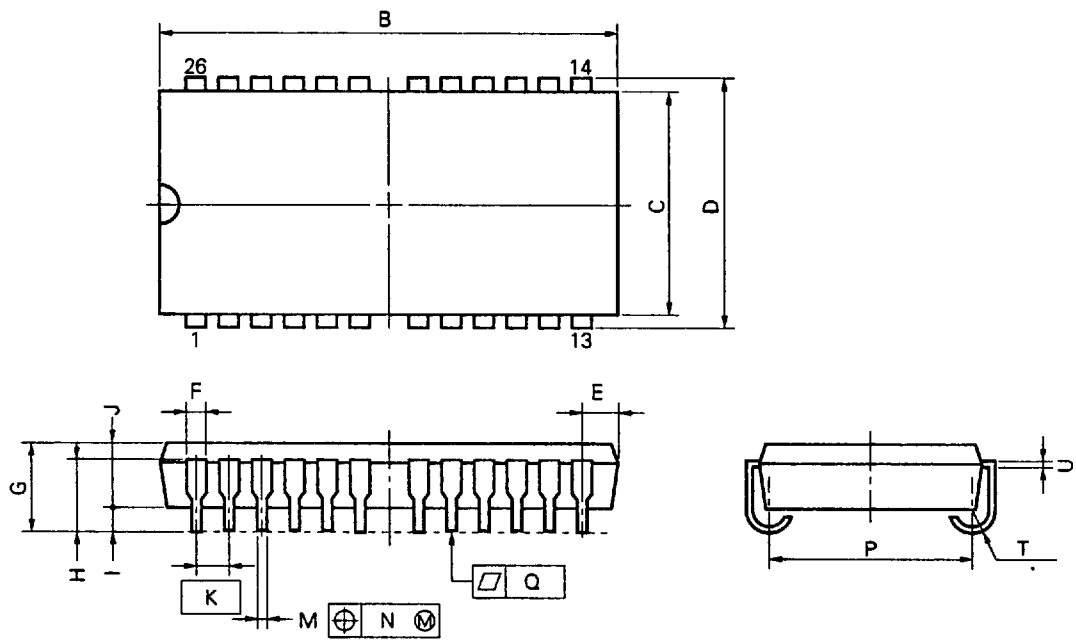
* : under development

PAGE(S) INTENTIONALLY BLANK

494

26 PIN PLASTIC SOJ (300mil)
24 Leads

NEC Cord:S26LA-300A



NOTE

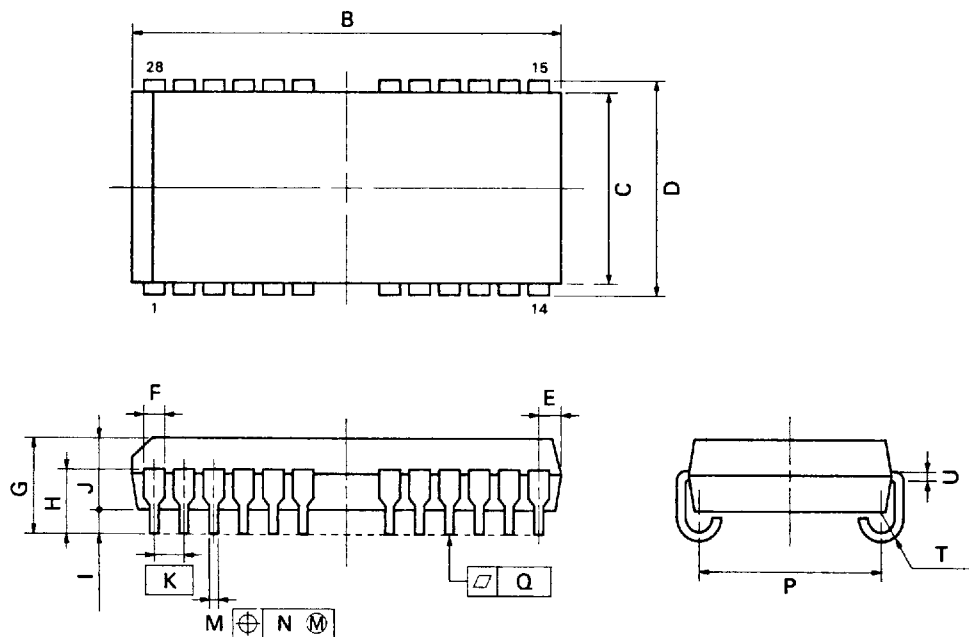
Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

S26LA-300A

ITEM	MILLIMETERS	INCHES
B	17.1 ^{+0.25} _{-0.05}	0.673 ^{+0.010} _{-0.002}
C	7.62	0.300
D	8.47±0.2	0.333 ^{+0.009} _{-0.008}
E	1.03±0.15	0.041 ^{+0.006} _{-0.007}
F	0.74	0.029
G	3.5±0.2	0.138±0.008
H	2.545±0.2	0.100±0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	0.016 ^{+0.004} _{-0.005}
N	0.12	0.005
P	6.73±0.20	0.265±0.008
Q	0.10	0.004
T	R 0.85	R 0.033
U	0.20 ^{+0.10} _{-0.05}	0.008 ^{+0.004} _{-0.002}

28 PIN PLASTIC SOJ (400mil)
24 Leads

NEC Cord:P28LE-400A



P28LE-400A

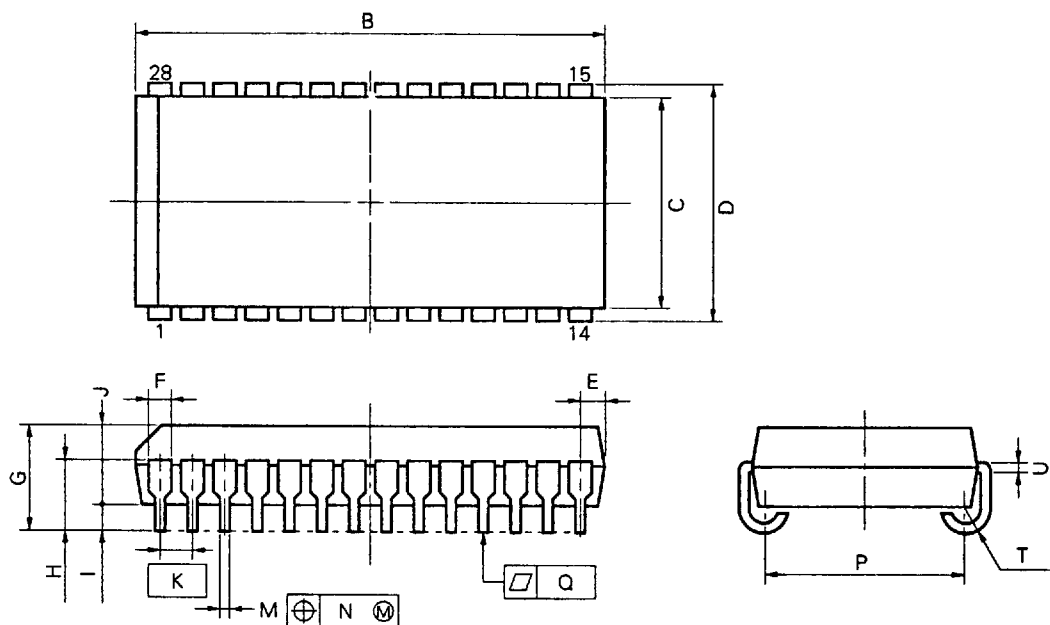
NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
B	18.67 ^{+0.25} _{-0.35}	0.735 ^{+0.008} _{-0.013}
C	10.16	0.400
D	11.18 ^{+0.2} _{-0.2}	0.440 ^{+0.008} _{-0.007}
E	1.08 ^{+0.15} _{-0.15}	0.043 ^{+0.006} _{-0.007}
F	0.7	0.028
G	3.5 ^{+0.2} _{-0.2}	0.138 ^{+0.008} _{-0.008}
H	2.4 ^{+0.2} _{-0.2}	0.094 ^{+0.008} _{-0.008}
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40 ^{+0.10} _{-0.10}	0.016 ^{+0.004} _{-0.004}
N	0.12	0.005
P	9.40 ^{+0.20} _{-0.20}	0.370 ^{+0.008} _{-0.007}
Q	0.15	0.006
T	R0.85	R0.033
U	0.20 ^{+0.10} _{-0.08}	0.008 ^{+0.004} _{-0.004}

28 PIN PLASTIC SOJ (400mil)
28 Leads

NEC Cord:P28LE-400A1



NOTE

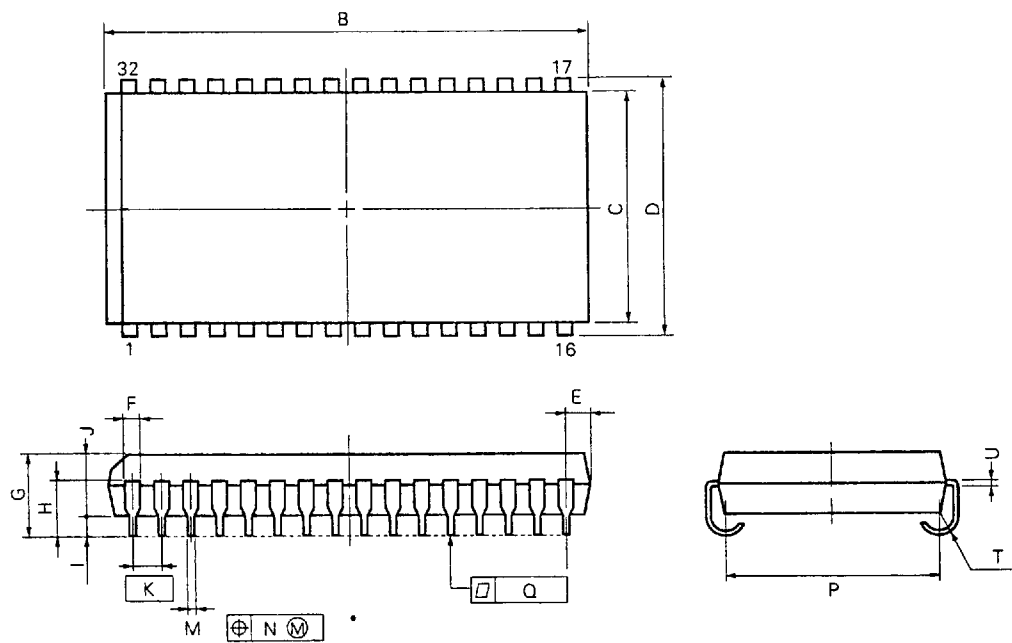
Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

P28LE-400A1

ITEM	MILLIMETERS	INCHES
B	$18.67^{+0.2}_{-0.35}$	$0.735^{+0.008}_{-0.013}$
C	10.16	0.400
D	11.18 ± 0.2	$0.440^{+0.008}_{-0.007}$
E	1.08 ± 0.15	$0.043^{+0.006}_{-0.007}$
F	0.74	0.029
G	3.5 ± 0.2	$0.138^{+0.008}_{-0.007}$
H	2.545 ± 0.2	0.100 ± 0.008
I	0.8 MIN	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40 ± 0.10	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	9.40 ± 0.20	$0.370^{+0.008}_{-0.007}$
Q	0.10	0.004
T	R 0.85	R 0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

32 PIN PLASTIC SOJ (400mil)

NEC Cord:P32LE-400A



NOTE

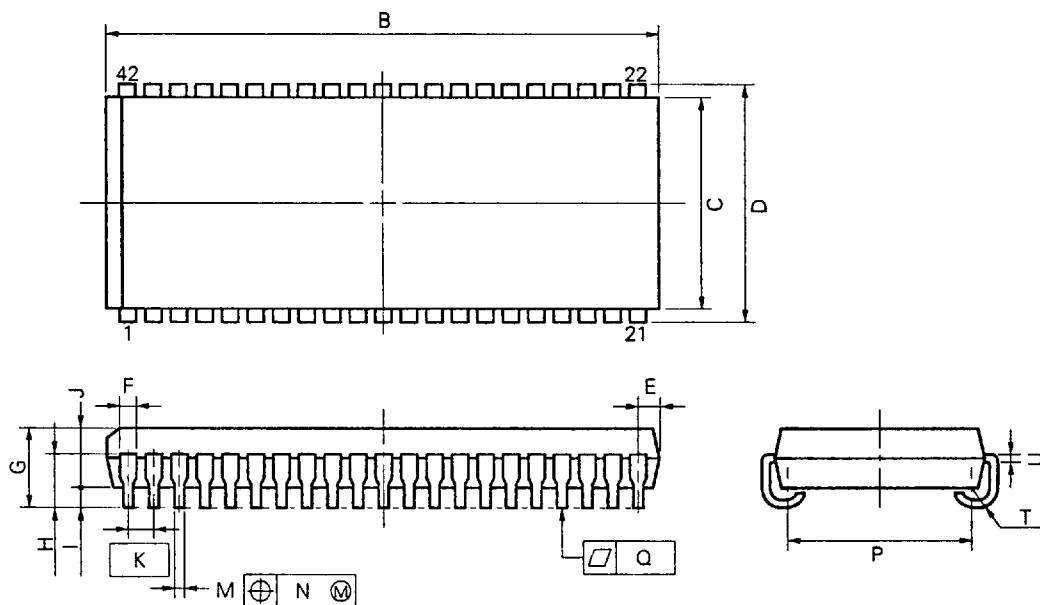
Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition

P32LE-400A

ITEM	MILLIMETERS	INCHES
B	21.06±0.2	0.829±0.008
C	10.16	0.400
D	11.18±0.2	0.440±0.008
E	1.005±0.1	0.040 ^{+0.004} _{-0.005}
F	0.74	0.029
G	3.5±0.2	0.138±0.008
H	2.545±0.2	0.100±0.008
I	0.8 MIN	0.031 MIN
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	0.016 ^{+0.004} _{-0.005}
N	0.12	0.005
P	9.4±0.20	0.370±0.008
Q	0.1	0.004
T	R 0.85	R 0.033
U	0.20 ^{+0.10} _{-0.02}	0.008 ^{+0.004} _{-0.002}

42 PIN PLASTIC SOJ (400mil)

NEC Cord:P42LE-400A

**NOTE**

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

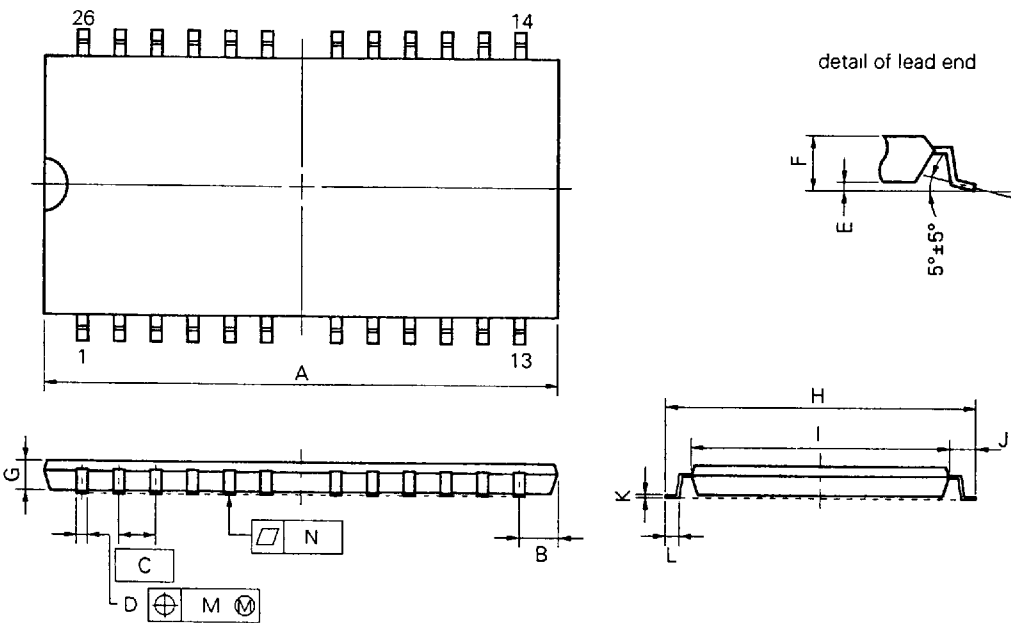
P42LE-400A

ITEM	MILLIMETERS	INCHES
B	$27.56^{+0.2}_{-0.35}$	$1.085^{+0.008}_{-0.014}$
C	10.16	0.400
D	11.18 ± 0.2	0.440 ± 0.008
E	1.08 ± 0.15	$0.043^{+0.006}_{-0.007}$
F	0.74	0.029
G	3.5 ± 0.2	0.138 ± 0.008
H	2.545 ± 0.2	0.100 ± 0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40 ± 0.10	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	9.4 ± 0.20	0.370 ± 0.008
Q	0.10	0.004
T	R 0.85	R 0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

26 PIN PLASTIC TSOP (300mil) *
 24 Leads

* : under development

NEC Cord:S26G3-50-7JD



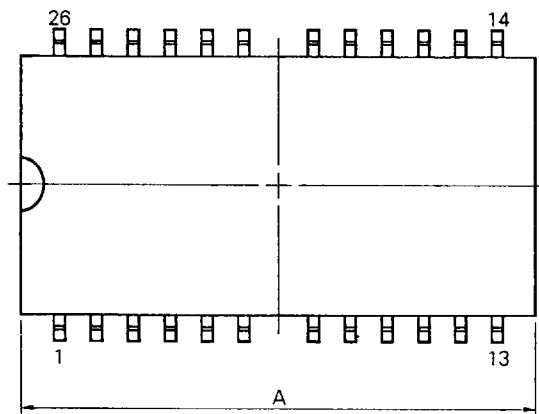
NOTE
 Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S26G3-50-7JD		
ITEM	MILLIMETERS	INCHES
A	17.40 MAX.	0.685 MAX.
B	1.06 MAX.	0.042 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40±0.10	0.016 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	9.22±0.2	0.363±0.008
I	7.62±0.1	0.300±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.21	0.009
N	0.10	0.004

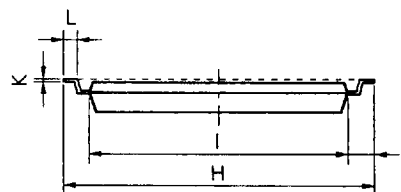
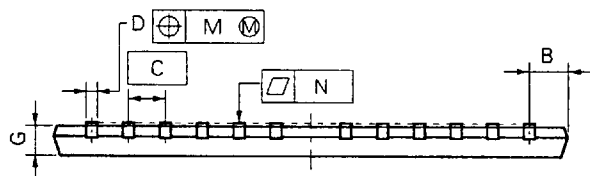
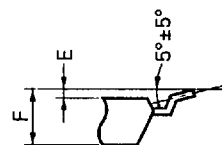
26 PIN PLASTIC TSOP (300mil) *
24 Leads Reverse bent

* : under development

NEC Cord:S26G3-50-7KD



detail of lead end



S26G3-50-7KD

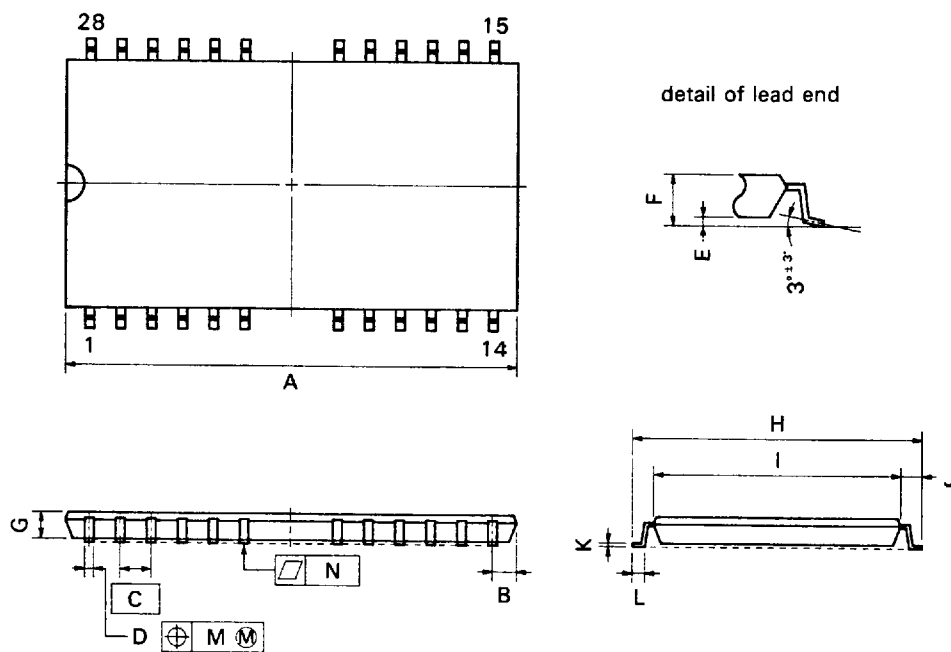
NOTE

Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P) at maximum material condition

ITEM	MILLIMETERS	INCHES
A	17.40 MAX.	0.685 MAX.
B	1.06 MAX.	0.042 MAX.
C	1.27 (T P)	0.050 (T.P.)
D	0.40±0.10	0.016 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	9.22±0.2	0.363±0.008
I	7.62±0.1	0.300±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.1	0.020 ^{+0.004} _{-0.005}
M	0.21	0.009
N	0.10	0.004

28 PIN PLASTIC TSOP (400mil)
24 Leads

NEC Cord:S28G5-50-7JD1



NOTE

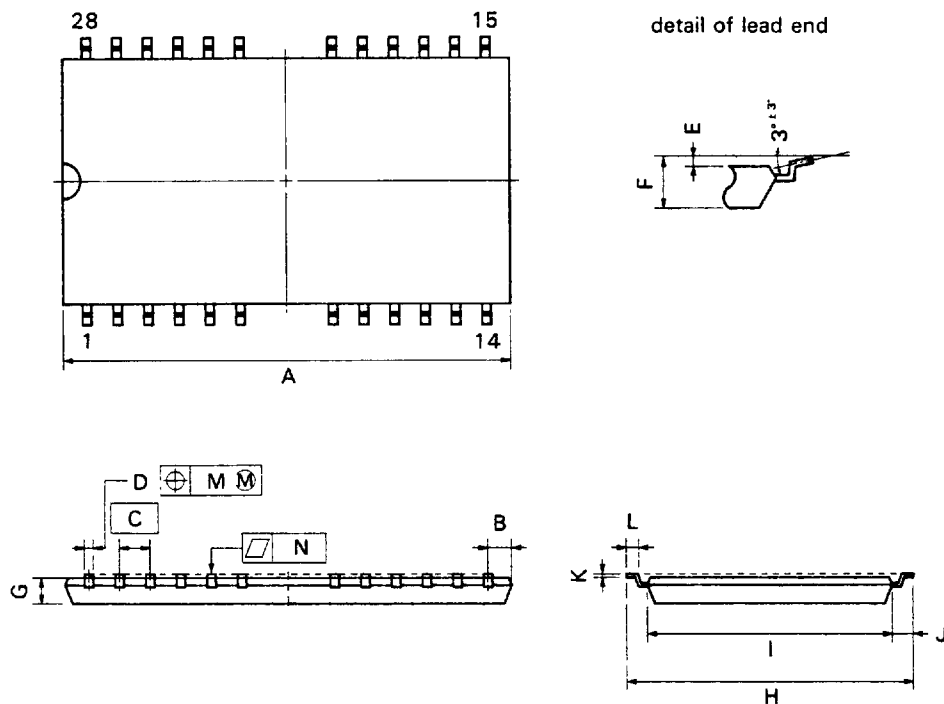
Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S28G5-50-7JD1

ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.15 MAX.	0.046 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40 ± 0.10	0.016 ± 0.004
E	0.05 ± 0.05	0.002 ± 0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76 ± 0.2	0.463 ± 0.008
I	10.16 ± 0.1	0.400 ± 0.004
J	0.8 ± 0.2	0.031 ± 0.008
K	0.125 ± 0.10	0.005 ± 0.004
L	0.5 ± 0.1	0.020 ± 0.004
M	0.21	0.009
N	0.10	0.004

28 PIN PLASTIC TSOP (400mil)
24 Leads Reverse bent

NEC Cord:S28G5-50-7KD1



NOTE

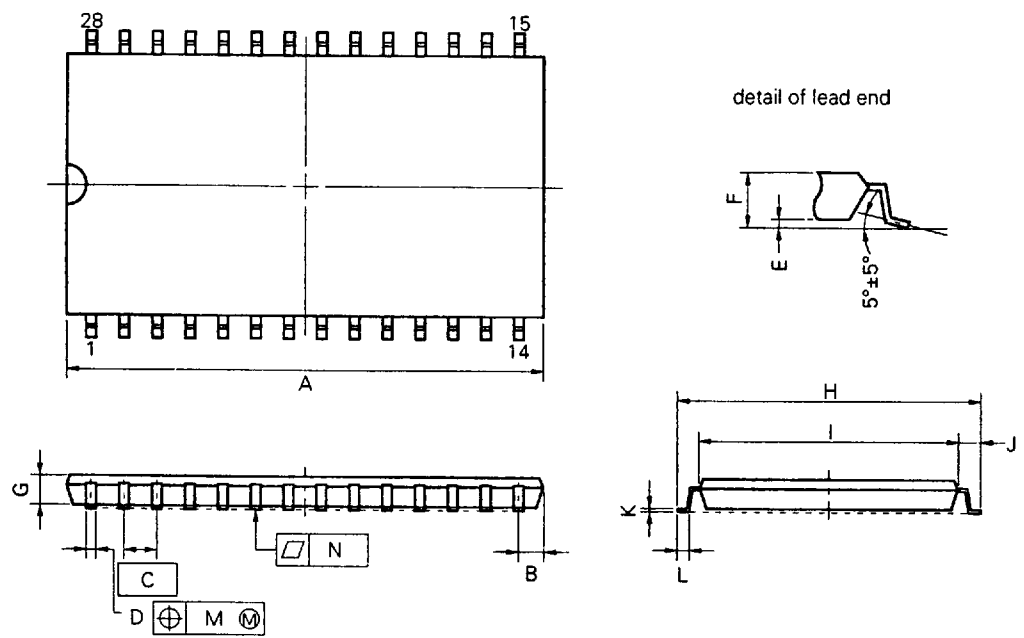
Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S28G5-50-7KD1

ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.15 MAX.	0.046 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40 ± 0.10	0.016 ± 0.004
E	0.05 ± 0.05	0.002 ± 0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76 ± 0.2	0.463 ± 0.008
I	10.16 ± 0.1	0.400 ± 0.004
J	0.8 ± 0.2	0.031 ± 0.008
K	0.125 ± 0.02	0.005 ± 0.001
L	0.5 ± 0.1	0.020 ± 0.004
M	0.21	0.009
N	0.10	0.004

28 PIN PLASTIC TSOP (400mil)
28 Leads

NEC Cord:S28G5-50-7JD2

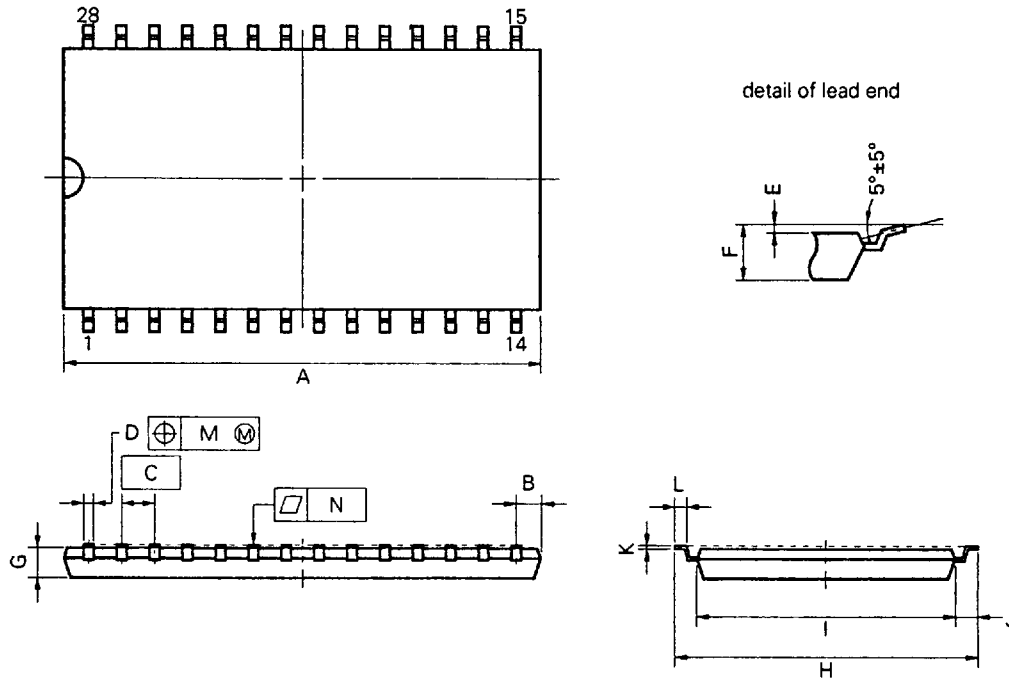


NOTE
Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S28G5-50-7JD2		
ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.15 MAX.	0.046 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40±0.10	0.016 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.15	0.020 ^{+0.006} _{-0.007}
M	0.21	0.009
N	0.10	0.004

28 PIN PLASTIC TSOP (400mil)
28 Leads Reverse bent

NEC Cord:S28G5-50-7KD2



NOTE

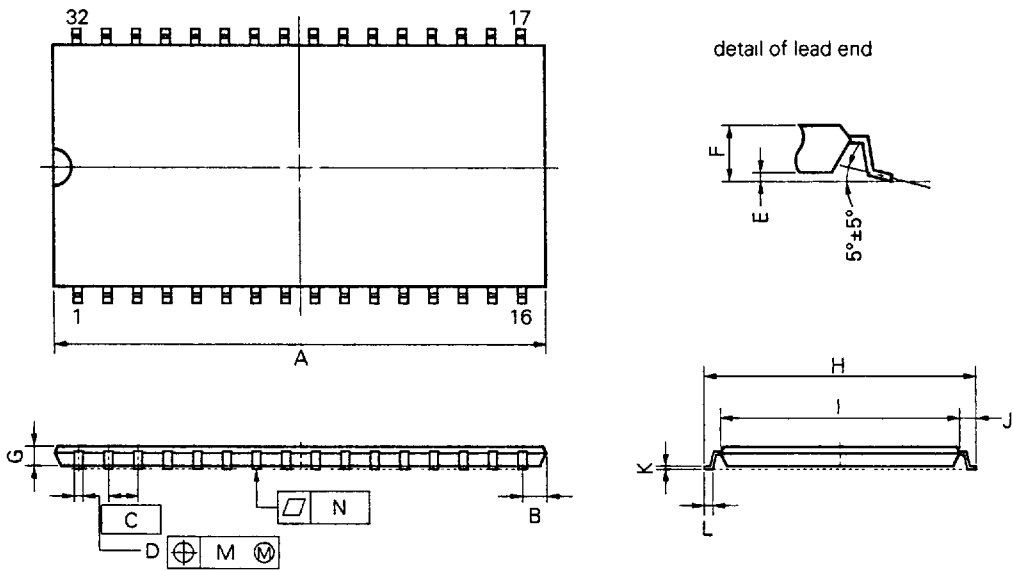
Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S28G5-50-7KD2

ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.15 MAX.	0.046 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40±0.10	0.016 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.15	0.020 ^{+0.006} _{-0.007}
M	0.21	0.009
N	0.10	0.004

32 PIN PLASTIC TSOP (400mil)

NEC Cord:S32G5-50-7JD1

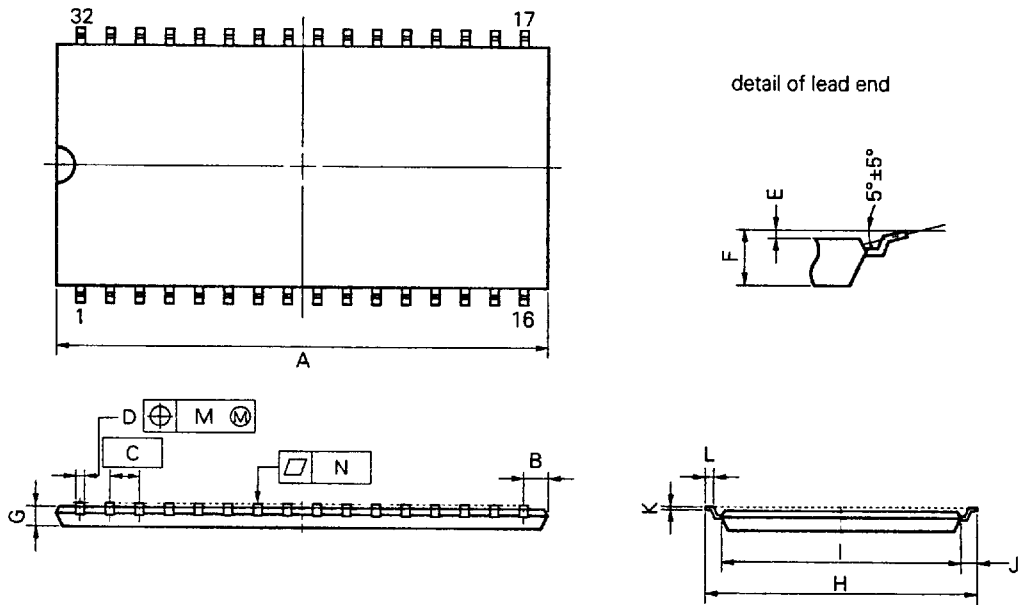


NOTE
Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S32G5-50-7JD1		
ITEM	MILLIMETERS	INCHES
A	21.17 MAX.	0.834 MAX.
B	1.06 MAX.	0.042 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40±0.10	0.016 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.15	0.020 ^{+0.006} _{-0.007}
M	0.21	0.009
N	0.10	0.004

32 PIN PLASTIC TSOP (400mil)
Reverse bent

NEC Cord:S32G5-50-7KD1

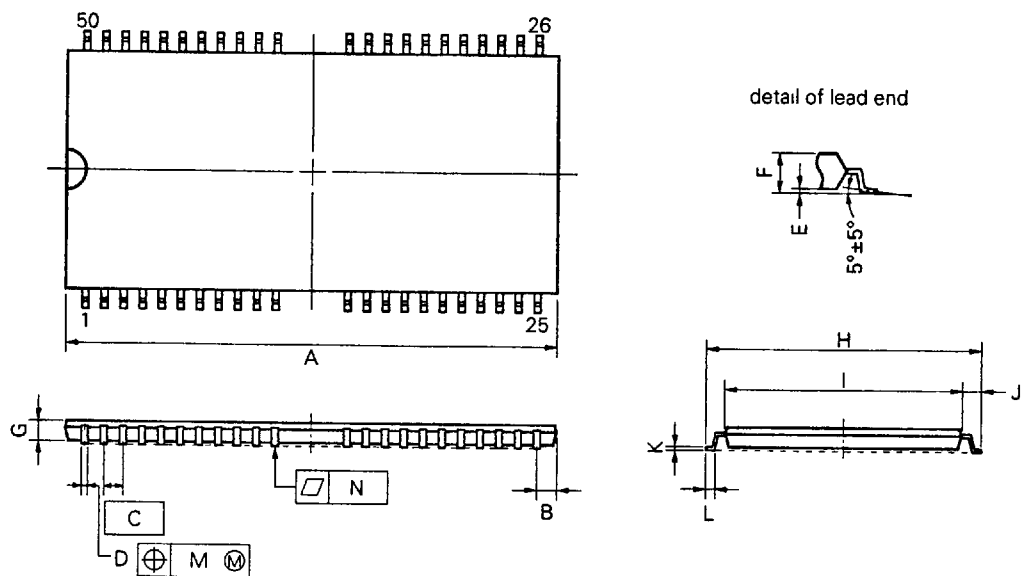


NOTE
Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

S32G5-50-7KD1		
ITEM	MILLIMETERS	INCHES
A	21.17 MAX.	0.834 MAX.
B	1.06 MAX.	0.042 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40±0.10	0.016 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.15	0.020 ^{+0.006} _{-0.007}
M	0.21	0.009
N	0.10	0.004

50 PIN PLASTIC TSOP (400mil)
44 Leads

NEC Cord:S50G5-80-7JF

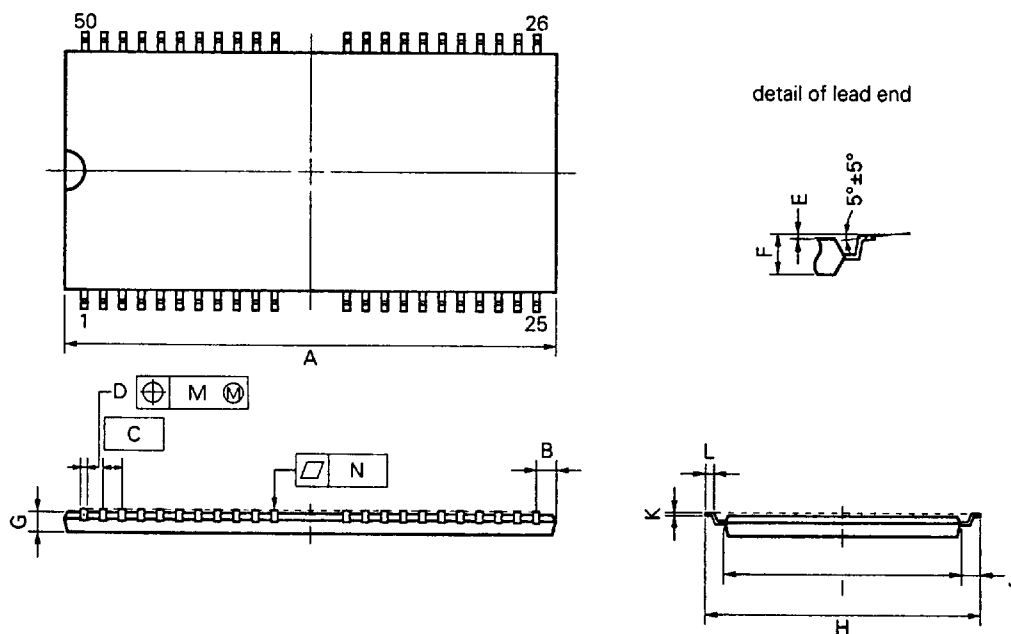


NOTE
Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

S50G5-80-7JF		
ITEM	MILLIMETERS	INCHES
A	21.45 MAX.	0.845 MAX.
B	1.13 MAX.	0.045 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.30±0.10	0.012 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.15	0.020 ^{+0.006} _{-0.007}
M	0.13	0.005
N	0.10	0.004

50 PIN PLASTIC TSOP (400mil)
44 Leads Reverse bent

NEC Cord:S50G5-80-7KF



NOTE

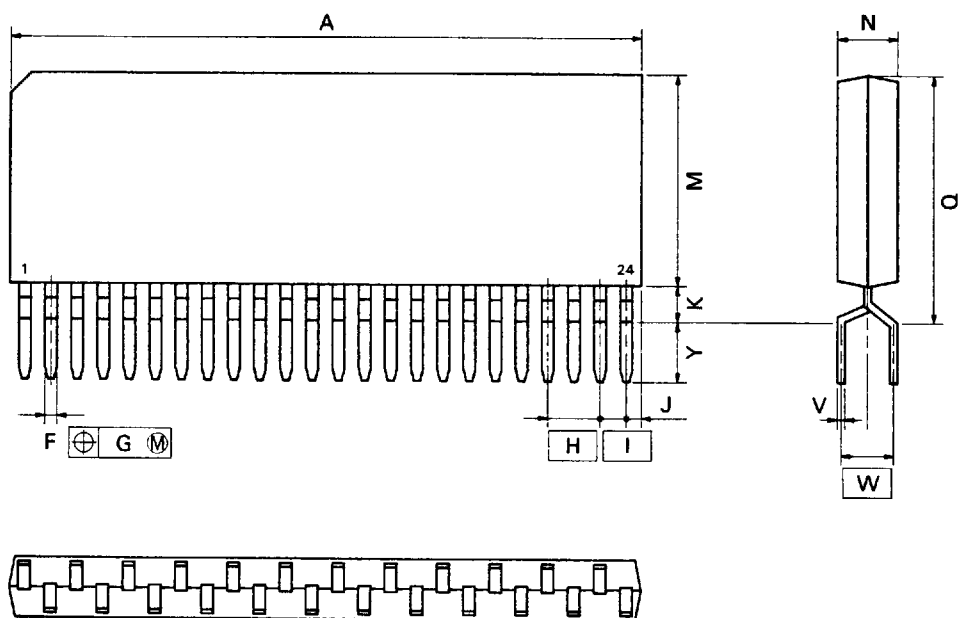
Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

S50G5-80-7KF

ITEM	MILLIMETERS	INCHES
A	21.45 MAX.	0.845 MAX.
B	1.13 MAX.	0.045 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.30±0.10	0.012 ^{+0.004} _{-0.005}
E	0.05±0.05	0.002±0.002
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	0.031 ^{+0.009} _{-0.008}
K	0.125 ^{+0.10} _{-0.05}	0.005 ^{+0.004} _{-0.002}
L	0.5±0.15	0.020 ^{+0.006} _{-0.007}
M	0.13	0.005
N	0.10	0.004

24 PIN PLASTIC ZIP (475mil)

NEC Cord:P24V-100-475A



P24V-100-475A

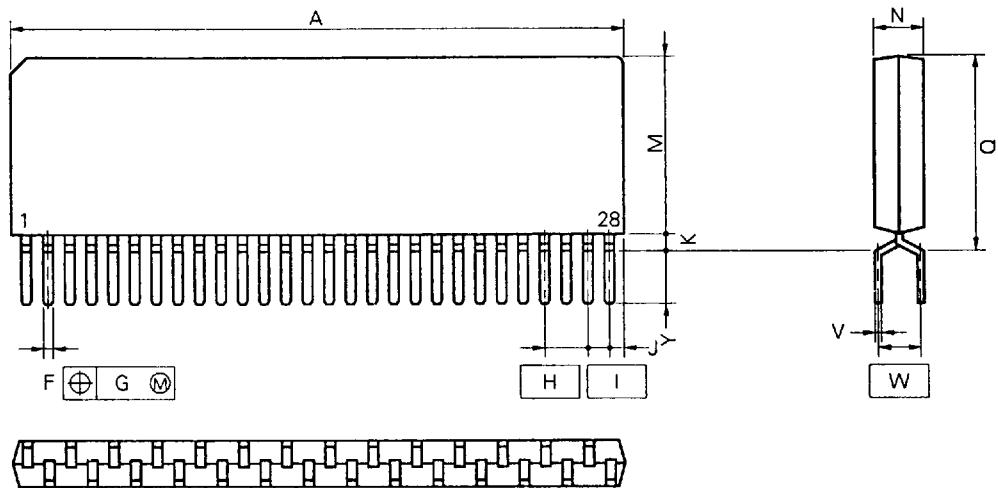
NOTE

Each lead centerline is located within 0.25 mm (0.010 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	31.75 MAX.	1.250 MAX.
F	0.50 ± 0.1	0.020 ± 0.004
G	$\phi 0.25$	$\phi 0.010$
H	2.54	0.100
I	1.27	0.050
J	1.27 MAX.	0.050 MAX.
K	1.0 MIN.	0.039 MIN.
M	10.8 MAX.	0.426 MAX.
N	2.8 ± 0.2	0.110 ± 0.008
Q	12.07 MAX.	0.476 MAX.
V	0.25 ± 0.10	0.010 ± 0.004
W	2.54	0.100
Y	3.3 ± 0.5	0.130 ± 0.02

28 PIN PLASTIC ZIP (475mil)

NEC Cord:P28VF-100-475A



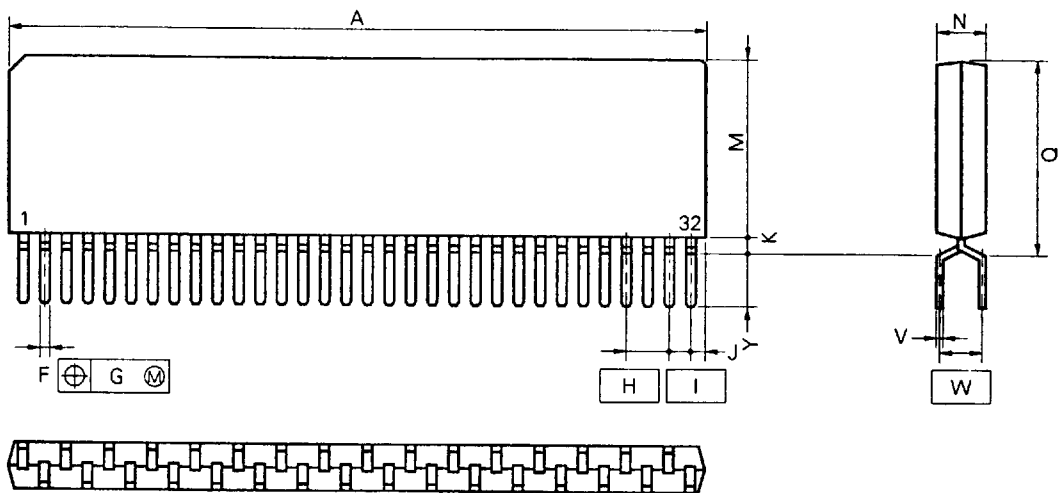
NOTE
Each lead centerline is located within 0.25 mm (0.010 inch) of its true position (T.P.) at maximum material condition.

P28VF-100-475A

ITEM	MILLIMETERS	INCHES
A	36.83 MAX.	1.450 MAX.
F	0.5±0.10	0.020 ^{+0.004} _{-0.005}
G	0.25	0.010
H	2.54 (T.P.)	0.100 (T.P.)
I	1.27 (T.P.)	0.050 (T.P.)
J	1.27 MAX.	0.050 MAX.
K	0.9 MIN.	0.035 MIN.
M	10.8 MAX.	0.426 MAX.
N	2.8±0.2	0.110 ^{+0.009} _{-0.008}
Q	12.07 MAX.	0.475 MAX.
V	0.25 ^{+0.10} _{-0.05}	0.010 ^{+0.004} _{-0.003}
W	2.54 (T.P.)	0.100 (T.P.)
Y	3.25±0.2	0.128±0.008

32 PIN PLASTIC ZIP (475mil)

NEC Cord:P32VF-100-475A



NOTE
Each lead centerline is located within 0.25 mm (0.010 inch) of its true position (T.P.) at maximum material condition.

P32VF-100-475A		
ITEM	MILLIMETERS	INCHES
A	41.91 MAX.	1.650 MAX
F	0.5±0.10	0.020 ^{+0.004} _{-0.005}
G	0.25	0.010
H	2.54 (T.P.)	0.100 (T.P.)
I	1.27 (T.P.)	0.050 (T.P.)
J	1.27 MAX.	0.050 MAX.
K	0.9 MIN.	0.035 MIN.
M	10.8 MAX.	0.426 MAX.
N	2.8±0.2	0.110 ^{+0.009} _{-0.008}
Q	12.07 MAX.	0.475 MAX.
V	0.25 ^{+0.10} _{-0.05}	0.010 ^{+0.004} _{-0.003}
W	2.54 (T.P.)	0.100 (T.P.)
Y	3.25±0.2	0.128±0.008